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MANUFACTURING METHODS AND TECHNOLOGY FOR TAPE CHIP CARRIER

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the determination of the associated yield and cost factors. This report includes an overview of these factors, the methods and equipment employed in the manufacture of approximately 1200 hybrid microcircuits with TAB, and the qualification test results of the circuits using the TAB mounted devices.

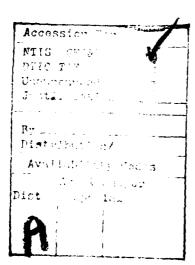


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INTRODUCTION

Tape Automated Bonding* (TAB) applications for military hybrid microcircuits have seen nearly five years of development. In the first several years, material combinations, bump and tape configurations and bonding techniques were explored under R&D contracts. Small to moderate quantities of different configurations were built and tested successfully. More recently emphasis was placed on the demonstration of production feasibility through Manufacturing Methods and Technology (MM&T) contracts.

The purpose of the MM&T work is to demonstrate the viability of the manufacturing approaches with TAB and the determination of the associated cost and yield factors. The established TAB manufacturing techniques included mounting of semiconductor chips on reels of sprocketed film or tape, burn-in and testing of these chips on tape and their placement on the hybrid substrates. The Army is interested in utilizing TAB technology for the manufacture of hybrid microcircuits for military electronic applications when advantageous for economic reasons or desirable from the viewpoint of increased reliability.

TAB technology can be implemented with a number of different materials and bonding technologies as described in the final reports of the R&D work**. At the start of the MM&T phase, specific selections of available materials and techniques were made, keeping in mind the requirements for performance and reliability. The process begins with a wafer in which all devices have gone through all the normally required semiconductor processing. The wafer is then given a protective cover of silicon nitride prior to the bumping process in order to more precisely define the bump geometry on the pads of each device and to offer greater protection of the chip surface. Barrier layer metallization of the pads on the semiconductor wafer consists of titanium, palladium and gold. The bump itself is plated of pure gold. The lead frame is electro-deposited copper, plated with 100 microinches of gold. The leads are thermocompression bonded to the bumps resulting in gold/gold bonds. The alumina substrates have been screen printed with mixed bonded gold paste. The outer lead bonds were thermocompression bonded, again resulting in gold/gold metallurgy. The chip is attached to a screened gold pad on the substrate with silver filled epoxy.

^{*}Also referred to as TCC (Tape Chip Carrier) and TCLF (Tape Carrier Lead Frame)

^{**}Reports ECOM-76-1401F, September 1977 and DELET-TR-2708F, September 1979 both entitled "Tape Chip Carrier for Hybrid Microcircuits".

This report is compiled as an overview of the methods and equipment employed in the successful manufacture of approximately 1,200 hybrid microcircuits with TAB technology. The manufacturing cycle included processing more than 10,000 chips, manufacturer and plating of 7,500 lead frames, inner lead bonding and testing of more than 6,000 chips on tape, and outer lead bonding of nearly 5,000 chips.

THE HYBRID MICROCIRCUIT

The hybrid is an 8 bit synchronous counter shift register consisting of two 54LS161A synchronous 4 bit counter chips, one 54LS165 parallel load 8 bit shift register chip and one capacitor chip. The hybrid will be referred to heareafter as the "E/M Sync Counter" or "SYNC Counter".

It is designed such that it is operational at its intended frequency of 18 MHz. Any or all 8 bit word patterns may be realized in the Sync Counter. Integrity of any 8 bit word is maintained in parallel load/transfer to the shift register. The 8 bit word, loaded in parallel, is shifted out of the register with the control gated serial clock. Serial data may be loaded into and out of the register with the control gated serial clock.

This hybrid is part of an Electrically Suspended Gyro (ESG) navigation system, currently being built in a quantity of several hundred systems, including the B-52 Navigation System, the Precision Navigation System (PNG) and one or more classified programs. A circuit schematic is shown in Figure 2-1. A photograph of the completed device is shown in Figure 2-2.

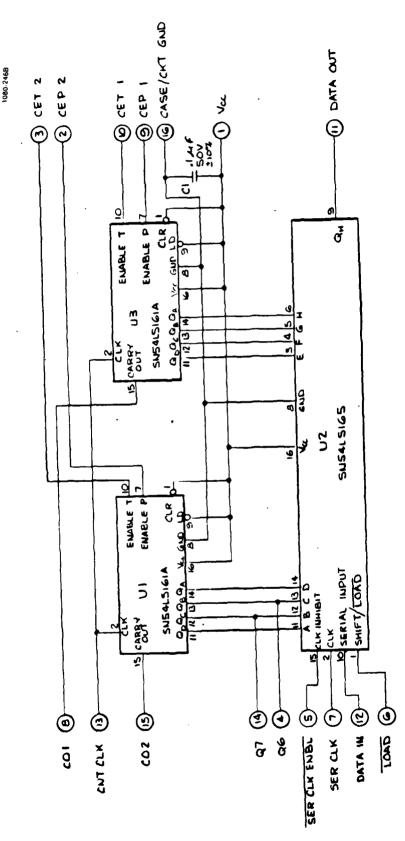


Figure 2-1. E/M Sync Counter Schematic

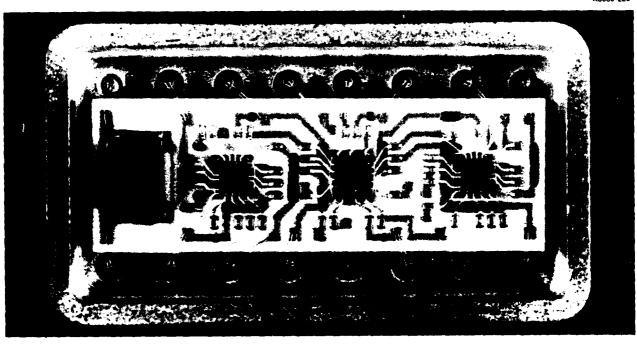


Figure 2-2. E/M Sync Counter After Assembly

THE ASSEMBLY SEQUENCE

Figure 3-1 shows schematically the assembly sequence as followed in the manufacture of the hybrids.

A substrate redesign/relayout took place as soon as basic circuit information became available. It was determined that the most economic screen printing configuration was a 14-up format on a 2x2 inch substrate (see Figure 3-2). The 2x2 substrates were prescribed by laser at P/M Industries in Portland Oregon, in order to allow breaking into individual substrates.

The semiconductor wafers were passivated with $\mathrm{Si}_3\mathrm{N}_4$ at Honeywell's Colorado Springs facility, followed by barrier layer metallization at Honeywell SSEC in Plymouth, Minn. Bumping was done at Honeywell Avionics Division (AvD) in Florida, with established solid photoresist (Riston 211) lamination method.

Lead frame design and production of 1:1 art was done per established methods at AvD in Florida. Lead frames were manufactured by Honeywell's Phoenix facility (LISD). Plating was accomplished on our newly installed continuous plater in Florida at a rate of 1000 frames/hour. Inner lead bonding (ILB) was done on the Jade I-1000 automatic bonder, at a rate of 1000 per hour. Chips were handled on continuous reels of tape through inner lead bonding and testing.

Testing of chips on tape was to be accomplished with the new Automatic Test Handler which has been on order from the Jade Corporation but was not delivered in time for this program. The manual reel-to-reel tester was used, allowing only room temperature testing. Test rates of up to 400 chips per hour were achieved while interfaced with the Fairchild 5000 automatic tester.

After testing, the tape was cut into frames and mounted into 35mm slide carriers (see Figures 3-3 and 3-4), designed and patented by Honeywell. A quantity of devices was tested after burn-in on the working portion of the Automatic Test Handler, which was mounted on a temporary base. (See Figure 8-6).

In preparation of outer lead bonding (OLB) the 2x2 substrates were screen printed with epoxy for chip attach (see Figure 3-5).

Outer lead bonding (OLB) was accomplished on the Jade 4810 machine at a rate of about 60 cnips per hour. Initially the 2x2 substrate (14-up configuration) was mounted in the substrate holder and populated, placing rows of 161A and 165 chips (see Figure 3-6). After a problem with substrate cracking caused unacceptable losses, the 2x2 substrate was broken into individual substrates (Figure 3-7) which were bonded one at a time in a special holder (see Figure 3-8). rate for this operation dropped to about 40 chips per hour. The approach to use a 14-up configuration on a 2x2 substrate can be used in future projects if precautions are taken with regard to substrate flatness and proper seating in the holder. Minor modification in the holder may be required. Trial bonds of the prelaser scribed substrates were performed without difficulty during test set-up. However, frequency/rep.rate of laser and/or power output of the laser to work surface was altered by the vendor causing heat build up and microcracking of substrates actually used in this work resulting in difficulties observed. It is not anticipated that properly scribed substrates would result in further difficulties of this nature.

After OLB the populated substrate was mounted in the header, the capacitor was added, followed by pin-out bonding with conventional thermosonic bonding techniques. The completed TAB Sync Counter is shown in Figure 2-2. As comparison, a wire bonded (conventional) Sync Counter is shown in Figure 3-9.

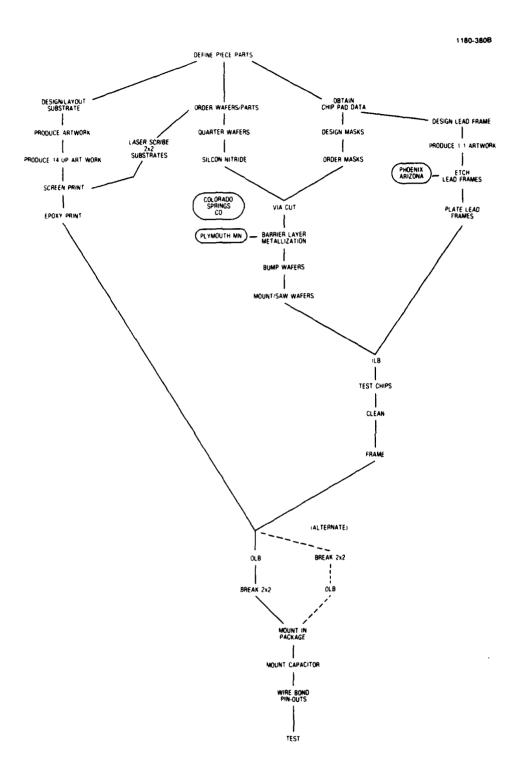


Figure 3-1. Assembly Sequence of E/M Sync Counter

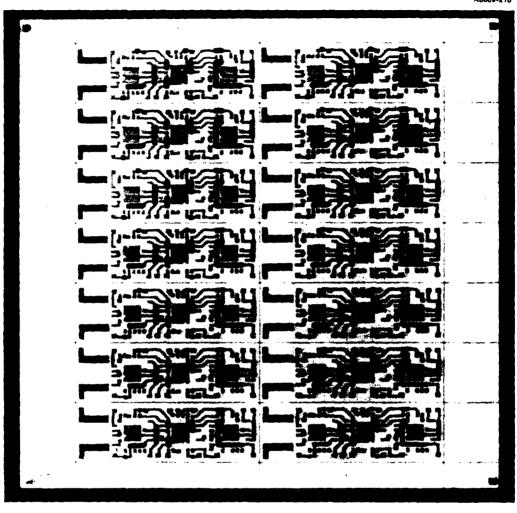


Figure 3-2. E/M Sync Counter as Screened - 14 Up

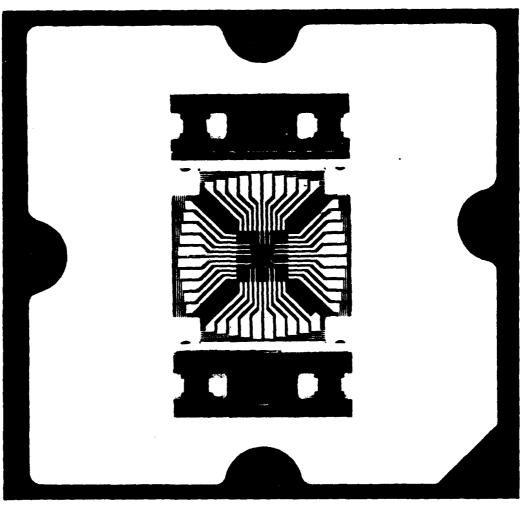


Figure 3-3. 54LS161A on Slide Carrier

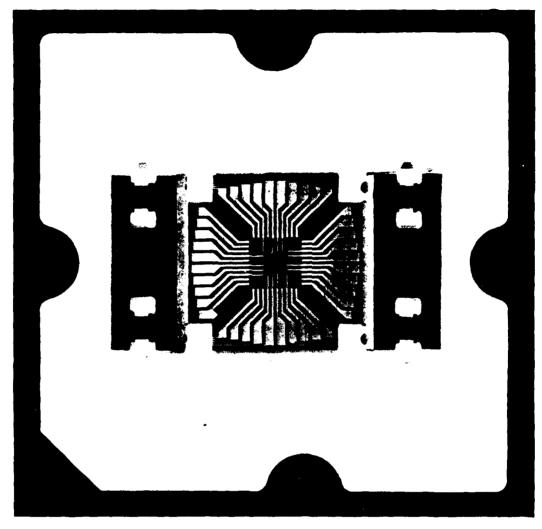


Figure 3-4. 54LS165 on Slide Carrier

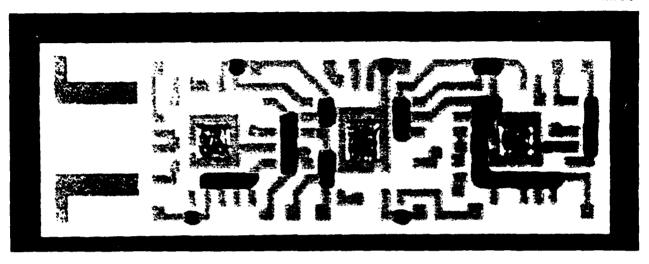


Figure 3-5. E/M Sync Counter After Epoxy Screen

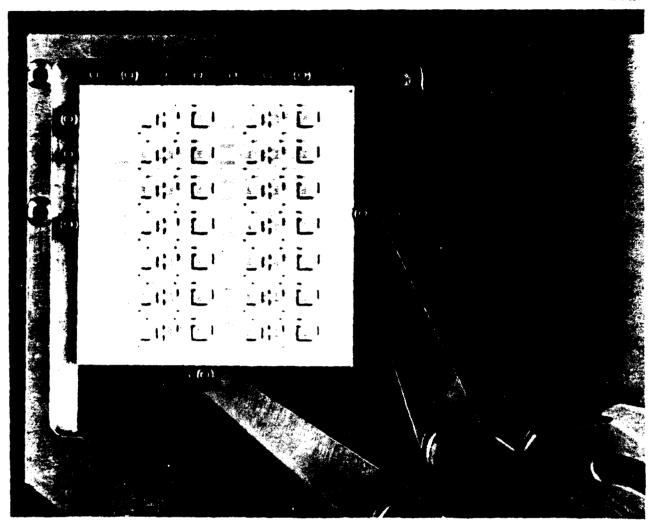


Figure 3-6. 2x2 Substrate in OLB Holder

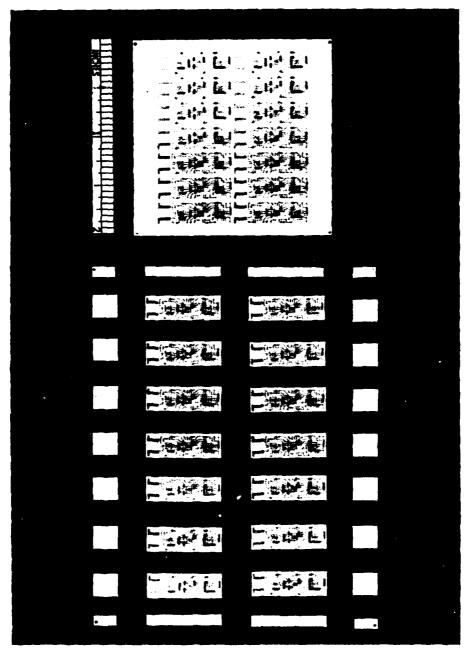


Figure 3-7. Break-up of 2x2 Substrate

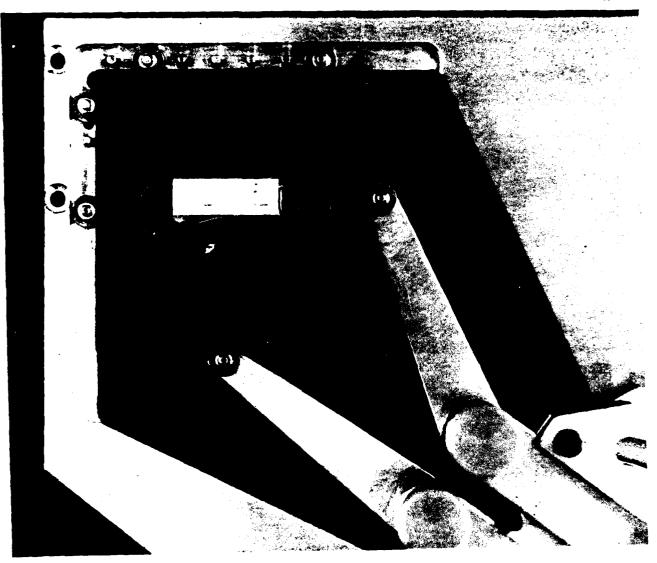


Figure 3-8. Single Substrate in OLB Holder

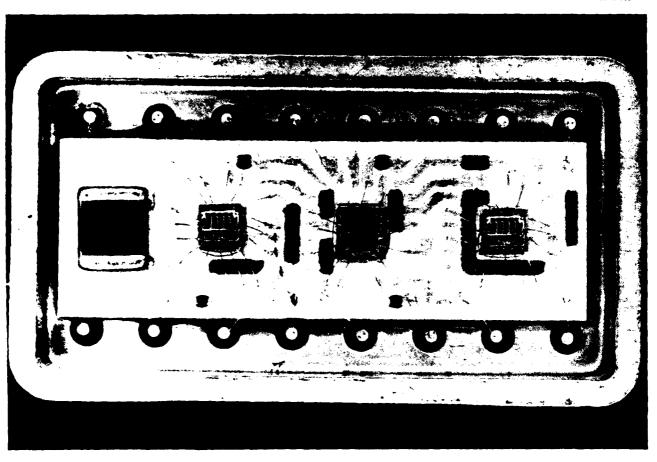


Figure 3-9. Wire Bonded Sync Counter

TAPE MANUFACTURE/PURCHASING

Lead frame tape (Figure 4-1) has been available to AvD from our LISD plant in Phoenix, where automatic equipment exposed and etched the purchased laminate (copper on prepunched polyimide). Approximately 10,000 frames have been produced during the course of this program. Because the LISD facility is set up to produce production quantities, no supply problems have been experienced. All tape used for this program is three-layer, 35mm wide polyimide, laminated to one ounce of electro deposited copper. All tape produced in Phoenix was plated with approximately 100 microinches of gold on the newly designed and installed continuous reel plater in our AvD facility in Clearwater (see Figures 4-2 and 4-3).



Figure 4-1. Typical 35mm Lead Frame Tape



Figure 4-2. Continuous Tape Plater

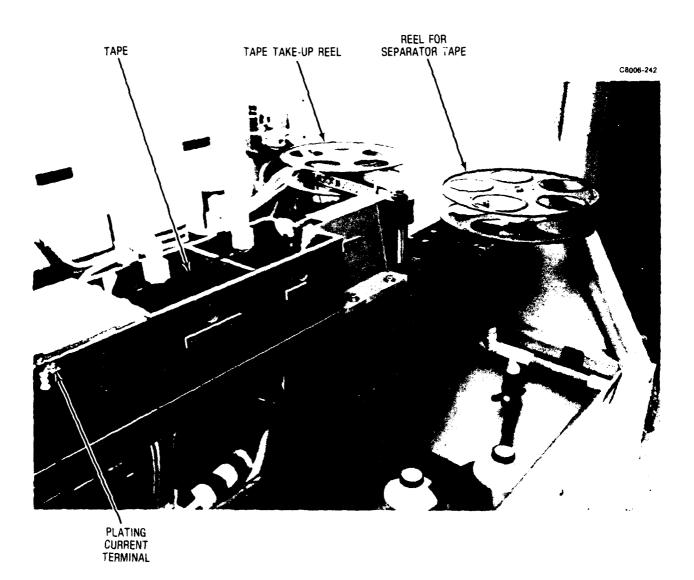


Figure 4-3. Continuous Tape Plater - Detail

WAFERS/CHIPS

Both 54LS161A and 54LS165 chips were purchased from Motorola on the format of 4-inch wafers. Because the processing equipment in Colorado Springs could not handle 4-inch wafers they were cut into quarters prior to processing (see Figure 5-1). Subsequent difficulty in handling this irregular format caused heavy losses at silicon nitride passivation and barrier layer metallization.

Figure 5-2 gives a schematic overview of the processing required and the respective locations of the wafer bumping process.

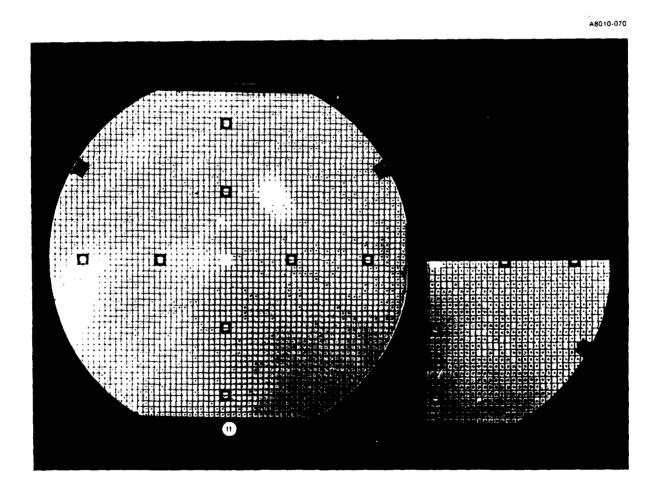


Figure 5-1. 4-inch Wafer/1/4 Wafer

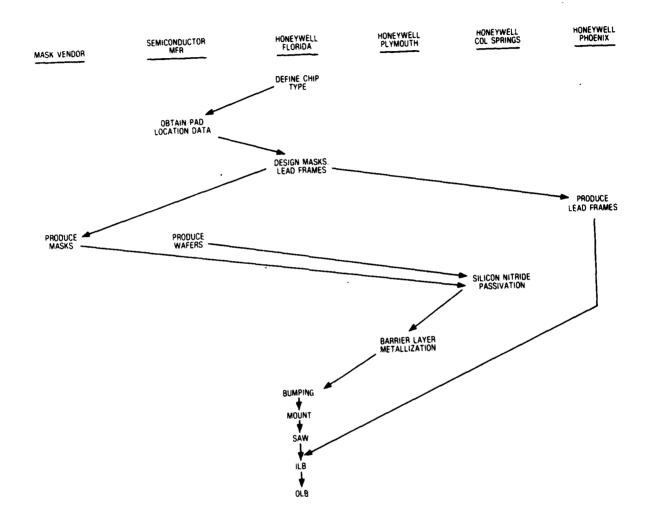


Figure 5-2. TAB Process Location Chart

DESIGN STANDARDS

The tape was designed per Honeywell Standards (later incorporated into ASTM 7E45 standard for 35mm TAB carrier tape) with 40 leads and 5mm aperture (see Figure 6-1). The OLB pattern was designed per the proposed Honeywell standard (see Figure 6-2). The lead forming profile is shown in Figure 6-3. An enlargement of a 161A chip on tape, prior to OLB, is shown in Figure 6-4, where the exact lead routing is clearly distinguishable.

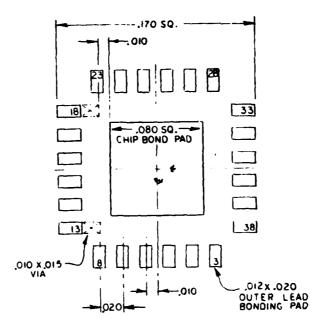
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PROBE POINTS (40 PLACES)

PLATING BUSES

ISOLATION PUNCH (4 PLACES)

Figure 6-1. Outer Portion of 35mm Tape Frame



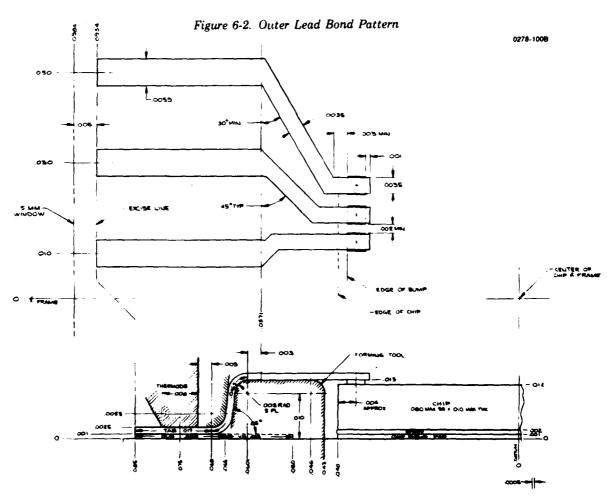


Figure 6-3. Lead Forming Profile

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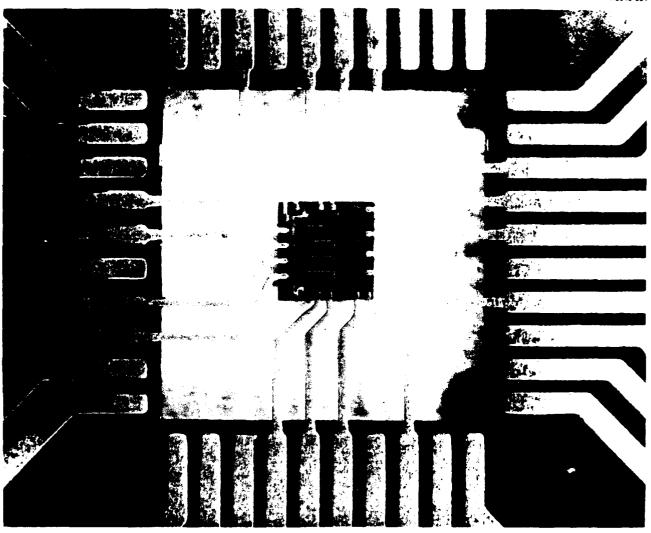


Figure 6-4. Close-up of 161A Chip on Tape

ELECTRICAL TESTING AND YIELDS

Yield figures are significant indications of the performance of the Sync Counter hybrid as an assembly vehicle to gauge the viability of the TAB-based assembly. Yield figures are derived at four basic operating points in the assembly and test sequence:

- 1. TAB preparation of wafers/cnips and TAB assembly operations
- 2. Hybrid assembly
- 3. Visual inspections
- 4. All electrical tests

An analysis of yields at each of these points has been made and is further discussed in this section.

1. TAB Operations Yields

The TAB operations in this portion of the analysis include barrier layer metallization and bumping, wafer mounting and sawing, Inner Lead Bonding (ILB), electrical test of chips on tape, visual inspection of the chips on individual slide carriers, and finally, Outer Lead Bonding (OLB). Table 7-1 shows these yields for both the 54LS161A and 54LS165 chips.

High losses at wafer barrier layer metallization were caused by the requirement to process quartered 4-inch wafers in equipment set up to automatically handle round 3-inch wafers.

Unusual losses at wafer mounting occurred when the lot of cement turned out to be aged, after a number of quarters were already mounted. These wafers could not be inner lead bonded.

2. Hybrid Assembly Yields

The hybrid assembly yield figure is determined by the ratio of substrates started versus substrates which successfully completed assembly. It therefore includes the OLB bonding operation, except it does not take into account the number of chips, which is shown in the previous section.

Table 7-2 shows the assembly yield on a lot by lot basis. The average assembly yield of all TAB lots was 87.5 percent, the CBI* lot was 100 percent and the chip and wire lot was 99 percent. The lower TAB assembly yield was caused by the substrate breakage problem, previously described in Section 3.

3. <u>Visual Inspections</u>

Visual inspections were carried out at two key points in the assembly sequence. The first, the Pre-Cap Visual inspection took place just prior to seal. The second or Final visual took place just before shipment.

Table 7-3 shows the inspection yields by lot, for each of the two inspection stations. The average yields of the Pre-cap Inspection for the TAB lots was 70.7 percent, for the CBI lot 87 percent and the chip-and-wire lot 86 percent. The relatively low figure for the TAB lots was artificially created by the new and untried TAB accept/reject criteria, which were updated on several occasions. The average yields of the Final Visual Inspection for the TAB lots was 98.9 percent, for the CBI lot 100 percent and for the chip-and-wire lot 94 percent.

4. Electrical Test Yields

The most significant information with regard to the success of the TAB approach is obtained through analysis of the electrical test yields. Table 7-4 lists yields per lot for First Electrical test, ATP** at 25°C, -55°C and 100°C as well as total ATP yield for TAB, CBI and chip-and-wire devices. Lot 2 contains data taken both before and after burn-in of the hybrids in order to obtain a yield of the burn-in operation. Analysis of the First Electrical test yield data shown in Table 7-5 clearly shows the significant impact of TAB. The 86 percent yield is obtained because the chips were tested prior to assembly while mounted on tape. The 52 percent yield at the same point, of the conventional chip-and-wire devices, indicates the high losses of the final product mostly due to chips failing to meet operational specification limits. Please note that these chips originated from the same wafer as the TAB chips and were electrically wafer probe tested at the same time. Also significant is the even higher yield of the TAB devices whose chips were not only tested but also burned-in prior to assembly (CBI). This lot has an even higher first test yield of 93 percent due to marginal chips having been stressed and eliminated.

^{*}Chips burned-in prior to assembly.

^{**}Acceptance Test Procedure (Final).

Analysis of the ATP Electrical Tests verify the results with regard to the CBI log. Table 7-6 indicates no significant difference between the TAB and chip-and-wire devices, because the initially unoperative wirebonded chips were culled at the first electrical test. However, the marginally operative devices still escaped and were not eliminated until burn-in, therefore, the CBI lot displays the remarkably high yield of 90 percent at ATP test.

These data demonstrate that test and burn-in of chips on tape is not only feasible, but also highly profitable, and will be further manifested in significant reduction of troubleshooting, repair and retest of assembled devices.

5. Failure Analysis

A failure analysis was performed on a total of six devices. They were various electrical tests done in sequence. With exception of one device all failures were caused by chip processing defects, manifested at first electrical test. The Failure Analysis Report number 66-F covering the analysis in detail is attached as Appendix I to this report.

Table 7-1. Yield History of TAB Operations

Operation	<u>on</u>	(IC) 161A Qty.	Yield	(IC) 165 Qty •	Yield
Metal Bumping	IN: OUT:	5,560* 5,280	95 (62.5)*	2,421* 2,300	95(58.2)*
Wafer Mount/Sa	IN: OUT:	5,280 4,600	87.1	2,300 2,100	91.3
ILB	IN: OUT:	4,600 4,270	92.8	2,100 2,021	96.2
Elect Test	IN: OUT:	4,270 3,693	86.5	2,021 1,724	85.3
Visual on Car	rier IN: OUT:	3,693 3,371	91.3	1,724 1,596	92.6
OLB	IN: OUT:	3,371 2,910	86.3	1,596 1,355	84.9
Overall Yield	•		52.4		56.0

^{*} Previous experience with metallization and bumping of wafers has shown an approximate 95% yield from those processes. For this reason the quantities of dice shown as the number going "in" are calculated to indicate the number required to provide the number actually yielded coming "out". This was necessary because of the high losses experienced at those two processes due to necessity of manually handling quartered 4 inch wafers on equipment designed to automatically handle 3 inch wafers. The actual yields of 62.5% for 54LS161A chips and 58.2% for 54LS165 chips is substantially typical of the 95% figure which is based on data from processing of about 10,000 chips previously.

The actual number of 54LS161A chips committed to metallization/bumping in this effort was 8,448 and the number of 54LS165 chips was 3,946.

Table 7-2. Yield History of TAB Operations

Lot No.		Assembly
0001	In Out Yield	126 118 94%
0002	In Out Yield	126 111 88%
0003	In Out Yield	84 53 63%
0004	In Out Yield	126 81 64%
0005	In Out Yield	126 86 68%
0006	In Out Yield	126 86 68%
00υ7	In Out Yiela	126 112 89%
8000	In Out Yield	126 112 89%
0009	In Out Yield	126 122 97%
0010	In Out Yield	126 122 97%
0011	In Out Yiela	126 122 97%

Table 7-2. Yield History of TAB Operations (Continued)

Lot No.		Assembly
0012	In Out Yield	73 73 100%
0013	In Out Yield	126 122 97%
0014	In Out Yield	31 31 100%
CBI	In Out Yield	84 84 100%
Chip/Wire	•	155 152 98%

Table 7-3. Yield History of TAB Operations

Lot No.		Visual Inspection	Ext. Visual Final Inspection
0001	In	118	91
	Out	64	91
	Yield	54%	100%
0002	In	111	85
	Out	94	83
	Yield	85%	98%
0003	In	53	39
	Out	38	39
	Yield	72%	100%
0004	In	81	52
	Out	57	51
	Yield	70%	98%
0005	In	86	50
	Out	26	50
	Yield	30%	100%
0006	In	89	66
	Out	69	64
	Yield	77%	97%
0007	In	112	73
	Out	73	73
	Yield	65%	100%
8000	In	126	82
	Out	78	82
	Yield	62%	100%
0009	In	122	98
	Out	90	98
	Yield	74%	100%
0010	In	122	77
	Out	57	77
	Yield	47%	160%
0011	In	122	73
	Out	85	73
	Yield	70%	100%

Table 7-3. Yield History of TAB Operations (Continued)

Lot No.		Visual Inspection	Ext. Visual Final Inspection
0012	In	73	56
	Out	73	54
	Yield	100%	96%
0013	In	122	81
	Out	106	81
	Yield	87%	100%
0014	In	31	23
	Out	31	22
	Yield	100%	96%
CBI	In	84	69
	Out	73	69
	Yield	87%	100%
Chip/Wire		153 132 86%	66 62 948

Table 7-4. Yield History of TAB Operations

		lst	Final	Electric	al Test	Yields	
Lot No.		Electrical Test	ATP** @25°C		ATP @100°C		Shipped
0001	In Out Yield	118 99 84%	96 92 96%	92 91 99*	91 91 100%	95%	37
0002	In Out Yield	111 94 85%	89 86 97%	86 86 100%	86 85 99%	96%	35
0003	In Out Yield	53 47 89%	47 45 96ቄ	45 44 98%	44 39 89%	83%	39
0004	In Out Yield	81 62 76%	61 57 93%	57 56 98ቄ	56 52 93%	85%	37
0005	In Out Yield	86 77 89%	76 66 87%	66 65 99%	65 50 77%	66%	50
0006	In Out Yield	89 72 81%	72 71 99%	71 69 97%	69 66 96%	92%	65
0007		112 90 80%	89 89 100%	89 81 91%	81 73 90%	80%	73
8000	In Out Yield	125 116 93%	114 112 98%	112 106 95%	106 82 77%	72%	82
	In Out		94 90	90 90	90 89	0.50	

96%

Yield

100%

998

95%

^{*}Pre burn-in results Lot 0002 **Acceptance Test Procedure

Table 7-4. Yield History of TAB Operations

Final Electrical Test Yields

Lot No.		lst Electrical Test	ATP @25°C	ATP @-55°C	ATP @100°C	Total Yield	Shipped
0009	In Out Yield	122 110 90%	109 109 100%	109 105 96%	105 98 93%	90%	98
0010	In Out Yield	122 106 87%	104 104 100%	104 103 99%	103 77 75%	74%	77
0011	In Out Yield	122 107 88%	107 104 97%	104 100 96%	100 73 73%	68%	73
0012	In Out Yiela	73 67 92%	67 65 97%	65 63 97%	63 56 89%	84%	56
0013	In Out Yield	122 101 83%	95 93 98%	93 84 90%	84 81 96%	85%	81
0014	In Out Yield	31 27 87%	27 26 96%	26 26 100%	26 23 88%	85%	23
CBI	In Out Yield	84 78 93%	77 73 95%	73 72 99%	72 69 96%	90%	69
	In Out Yield	153 80 52%	73 73 100%	73 71 97%	71 66 93%	90%	64
	In Out Yield		80 75 94%	75 74 99%	74 73 99%	91%	

^{*}Pre burn-in results chip/wire.

Table 7-5. First Electrical Test Yields

	Oty In	<u>Rej</u>	ACC	Yield (%)
ТАВ	1367	192	1175	୪ 6
C/W	153	73	80	52
С.В.І.	84	6	78	93

Table 7-6. ATP Test Yields

	Qty In	Rej	Acc	Yield (%)
TAB	1158	212	946	82
C/W	80	14	66	83
C.B.I,	77	8	69	90

EQUIPMENT

The following TAB equipment and fixtures were used in the manufacturer of the Sync Counter hybrid microcircuit.

- Continuous Tape Plater Model No. STP, Microplate Inc. Used for reel-to-reel gold plating of copper lead frame material (see Figures 4-2 and 4-3).
- Inner Lead Bonder Model I-1000, The Jade Corp. Used to bond all chips to the lead frame tape (see Figure 8-1).
- Manual Tape Test Handler Model 001, The Jade Corp. Used to contact the chips on lead frame tape while electrically testing chips on the Fairchild 5000 (see Figure 8-2).
- Lead Frame Cutting Machine Model IIB, Seary Mfg Corp. Used to cut the lead frame tape into individual frames in preparation for slide carrier mounting (see Figure 8-3).
- Framing Fixture Model ME80C475, Honeywell Inc. Used to mount individual lead frames in standard slide carrier (see Figure 8-4).
- Burn-In Tank Model PSK 2922, Honeywell Inc. Used to burn-in chips on tape after ILB but prior to OLB (see Figure 8-5).
- Automatic Test Handler for Slide mounted tape frames (in Manual Mode) Model 5311, The Jade Corp. Used to test chips on tape after burn-in (see Figure 8-6).
- Outer Lead Bonder Model 4810, The Jade Corp. Used to excise, form, place and bond chip leads on the hybrid substrate (see Figure 8-7).
- Automatic Test Handler for Slide Mounted frames, Model 5311/S/N 1, the Jade Corp. (see Figure 8-8).

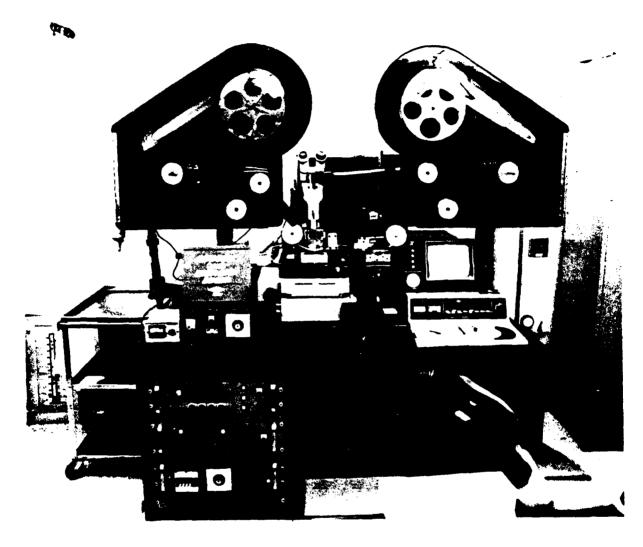


Figure 8-1. Inner Lead Bonder (ILB) Jade I-1000

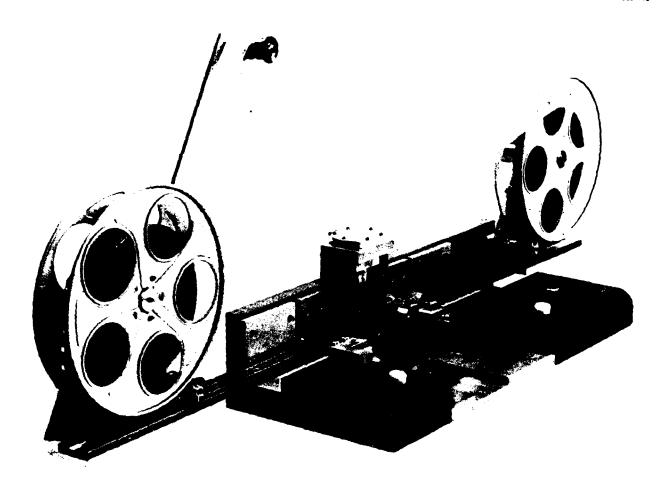


Figure 8-2. Manual Reel-to-Reel Tester Jade Model-001



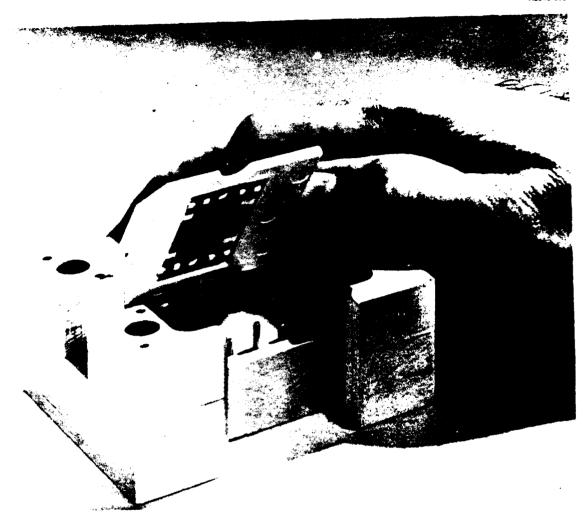


Figure 8-4. Framing Fixture

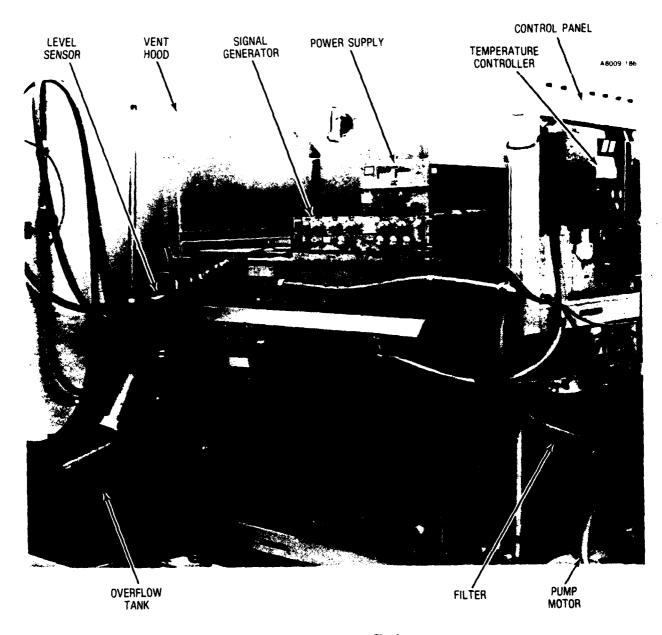


Figure 8-5. Burn-in Tank

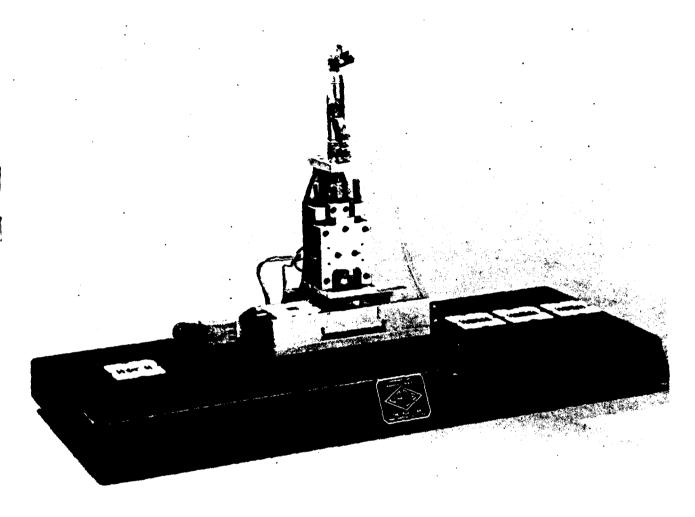


Figure 8-6. New Slide Tester on Temporary Base

A7805-135

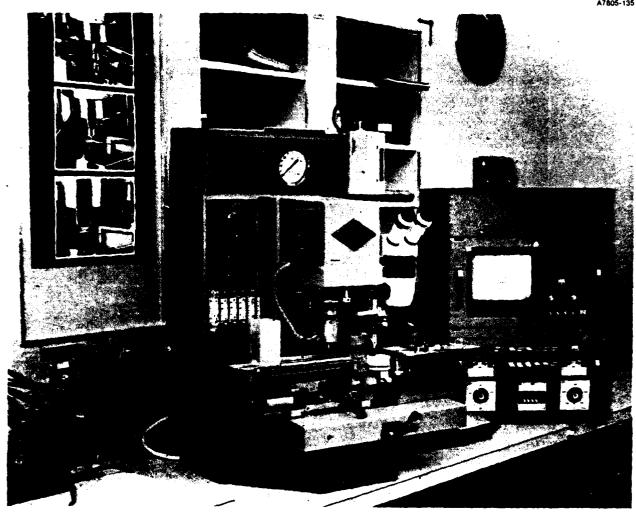


Figure 8-7. Jade 4810 Outer Lead Bonder



Figure 8-8. Automatic Test Handler for Slide Mounted Tape Frames Jade 5311

BURN-IN

When burn-in is required for hybrid devices, they are normally subjected to this screen after completion of the entire assembly process. Burn-in of individual semiconductor chips and other components prior to assembly has not been practical. TAB technology made it possible to burn-in semiconductor chips prior to assembly, as they are electrically accessible on the tape. Because the burn-in screen is most effective for semiconductor parts, applying this screen to the chips prior to assembly may, in many cases, alleviate the need for burning in the complete hybrid after assembly. Most importantly, however, it will reduce the amount of rework required after first electrical test.

The burn-in tank consists basically of an insulated reservoir filled with FC-43 which is heated, filtered and slowly circulated (see Figure 8-5). The slide carriers containing single tape frames with one chip each (Figure 9-1) are positioned on a tray having 96 positions (see Figure 9-2). The tray is married to an interconnect/ contact board containing POGO pins to contact the lead frame pads (see Figure 9-3). Figure 9-4 shows a close-up of the interconnect board with the spring loaded POGO pins and the aperture allowing free flow of fluorocarbon over the chip. The completed tray assembly (Figure 9-5) is then lowered into the tank and remains there for the required period (usually 168 hours), while the fluorocarbon is heated to the desired temperature, usually 125°C. Electrical signals to operate each device are fed into the tray through a connector Upon completion of the required burn-in time, the tray is assembly. removed and disassembled. The individual chips-on-tape then undergo electrical testing. The system can be adapted to burn-in any chip type by changing the 24 plug-in interconnect boards (Figure 9-6) each of which is designed to power a specific chip type.

Eighty-four circuits were fabricated from chips which had been burned in for 168 hours at 125°C. Because of a malfunction in the Test Handler, the chips could not be electrically tested following burn-in but all available burned-in chips on tape were committed to circuits. Yields from this lot are shown in Table 7-4 as lot number "CBI". As can be seen, the Total Yield of 90% was comparable to yields from other lots and would probably have been significantly higher had testing of chips on tape following burn-in been possible.

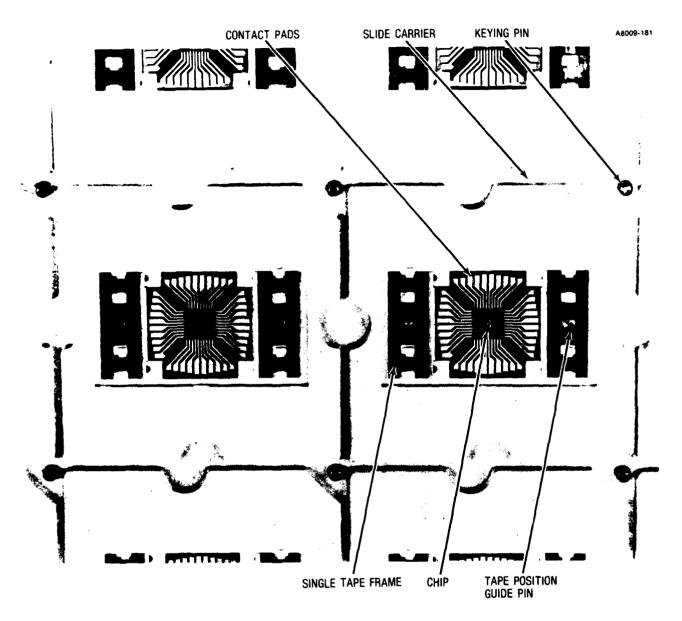


Figure 9-1. Chip on Single Frame Mounted in Slide Carrier

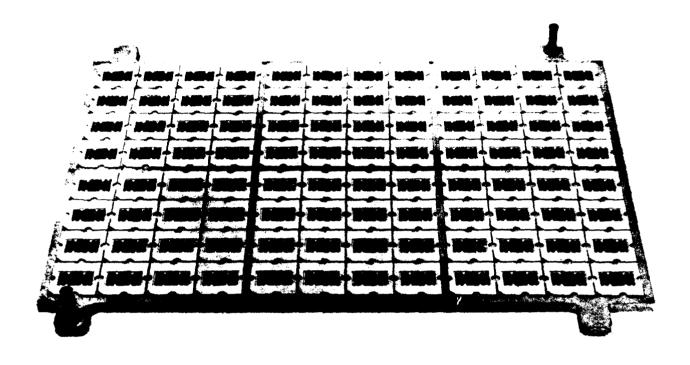


Figure 9-2. Burn-in Tray Populated with 96 Slide Carriers Prior to Assembly

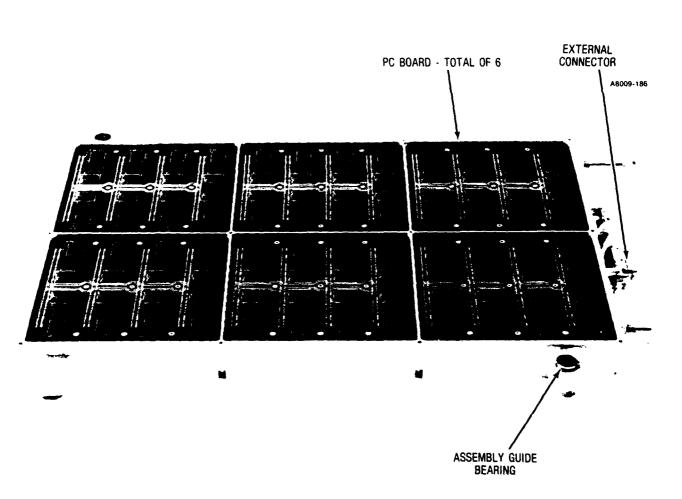


Figure 9-3. Interconnect Board Assembly

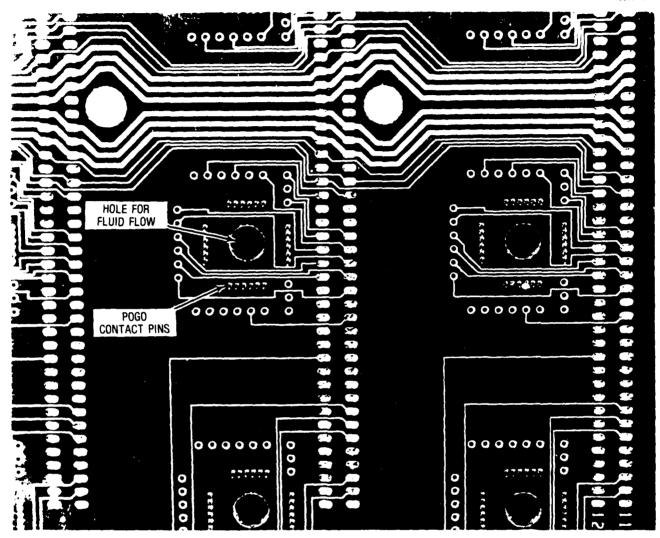


Figure 9-4. Interconnect PC Board Detail

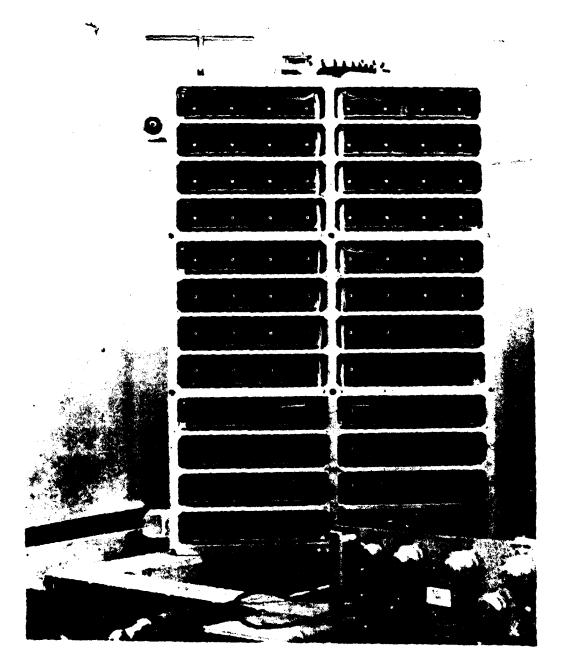


Figure 9-5. Loaded and Assembled Tray Ready For Insertion in Fluid

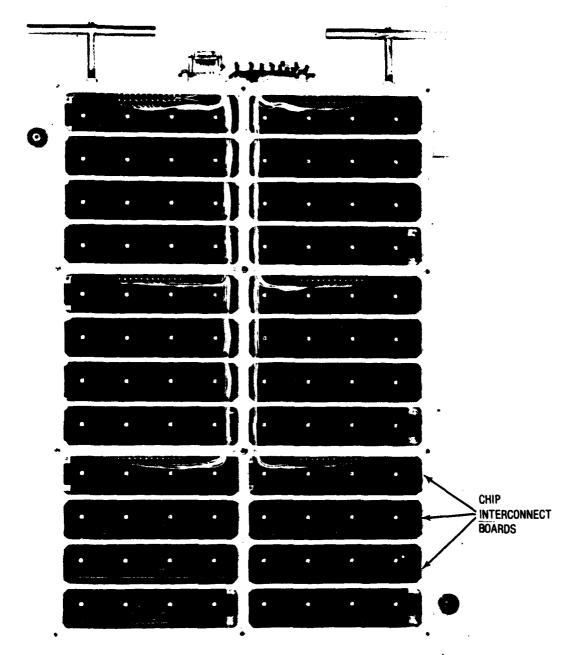


Figure 9-6. Burn-in Tray With Vertical Chip Interconnect Board

QUALIFICATION

The TAB E/M Sync Counter hybrid has been subjected to a military-type qualification program, which has tested every aspect of the performance capability of the device. With relatively minor exceptions the TAB hybrid has passed these qualification tests in a truly remarkable way.

The qualification program, including prior environmental screening steps is shown in detail on Figure 10-1. The qualification program consisted of five basic elements as follows: (Figure 10-2)

- A qualification test program based on the Patriot Fuze Program requirements and imposed by U.S. Army ERADCOM for the completed hybrid devices.
- 2. A stringent qualification program as required by the USAF B-52 retrofit program and imposed on Honeywell Hybrid devices.
- 4. Qualification of materials prior to assembly.
- Qualification of TAB equipment on a daily basis during assembly.

Items 1 and 2 are based on MIL-STD-883, Method 5008 Group B, C and D testing and are highlighted in Figures 10-1 and 10-3 as ERADCOM/Honeywell tests. The qualification requirements (quantity of devices and limits) are combined into one set of tests. A total of 81 devices were subjected to the different portions of the qualification program. Table 10-1 lists the device serial numbers and their respective lots for each of the Group B, C and D tests.

Device Qualification Results

The TAB hybrids have passed all but two of the above listed qualification tests without a single failure.

The first of the two tests failed was the Group B Die Shear Test, in which 2 out of 3 chips in every one of the five packages failed to meet the strength limit. An analysis of the failed epoxy joint indicated a high porosity level in the epoxy, plus the absence of any evidence of contamination (see Analysis Report #V02907, Appendix II). An investigation into the assembly traveller and sequence revealed that the epoxy of several lots had been thinned in unauthorized fashion, and also that several lots of screen printed epoxy had been stored over the week-end prior to die attach (OLB). This could have caused partial curing of the epoxy and resulting low bond strength. It is interesting to note that even with the low strength die bonds, the devices still met all environmental qualification tests, including mechanical, vibration and constant acceleration. This confirms the earlier theoretical analysis (Report #DELET-TR-77-2708-F, September 1979) which indicated that die attach is not required for mechanical integrity in TAB devices.

The above discussed qualification results are considered extremely positive. It appears that the TAB devices are almost indestructable under a variety of environments and stresses.

The qualification test travelers and QIIs (Quality Inspection Instructions) as well as the printed out electrical test results are included in a report titled "Qualification Test Data" and is available at ERADCOM.

Material Qualifications

In addition to device (hybrid) qualification tests after assembly and test, qualification on parts and materials was performed prior to use in assembly. These included the following:

- 1. Substrate qualifications, consisting of thickness profiles, TAB bond tests on the thick film gold, and gold were bond pull strength tests.
- 2. Gold Paste Qualification Tests, consisting of adhesion tests and wire bond pull tests to check bondability of the gold.
- Qualification of epoxies used to bond the chips and capacitor to the substrate.

TAB Bond/Equipment Qualification

Prior to and during each day's assembly the TAB bonding equipment was qualified by bonding all leads of one chip followed by pull strength testing. Mean (X) and standard deviation (σ) were then calculated. If these values were such that X-3 was equal to or greater than 10 grams the ILB or OLB was qualified for the day's production.

Inspection Criteria

In order to be able to visually inspect the TAB bonds, some modifications had to be made to Honeywell's Microelectronics Workmanship Standard, U-ED23036. These modifications include: rejection of devices which exhibited less than 50% of the TAB lead width on either the chip and/or the substrate bonding pads, bonds where there is no evidence of tool impression; and on the substrate, where a TAB lead tail and any adjacent metallization is closer than 0.001 inch. Acceptable rework procedures include: circular or semicircular bond imprint on TAB lead made by the wire bond capillary tool, lead bonded on remaining portion of other lead, and wirebond on top of "bump" or wirebond in place of TAB lead.

Table 10-1. Device Assignment for Qualification Tests*

Group "B" - 13 Devices

Lot 0001: 258, 209, 277

Lot 0002: 386, 392, 401, 403, 404, 417, 421, 423, 428, 431

Group "C" - 38 Devices

Lot 0001: 201, 202, 4, 5, 6, 12, 14, 16, 18, 19, 20, 21, 25, 26, 228, 233, 35, 39, 40, 41, 42, 45, 49, 50, 56, 57, 61, 65, 66, 67, 70, 72, 73, 75, 76, 80, 81, 85

Group "D" - 15 Devices

Lot 0001: 286, 93, 94, 95, 99, 302, 303, 04, 05, 06, 08, 09, 13, 14, 15

Group "D" - S/G 2

S/N: 537, 546, 547, 549, 553, 554, 558, 559, 560, 562, 566, 568, 569, 571, 572

^{*}Results available in "Qualification Test Data" report at ERADCOM.

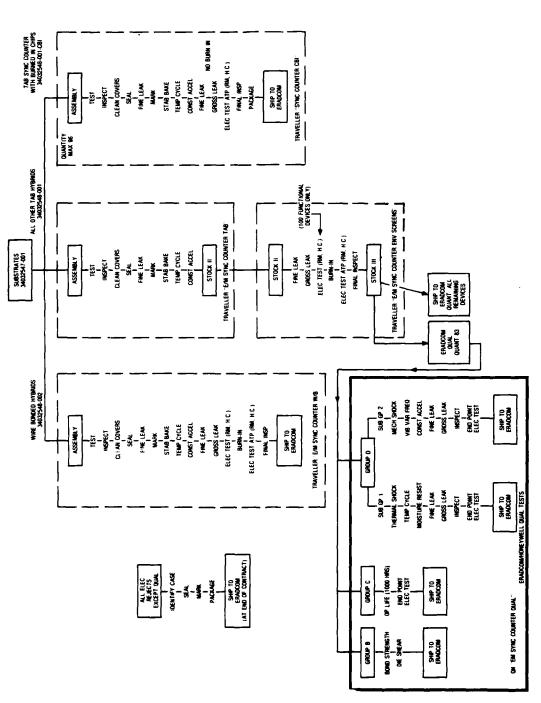


Figure 10-1. ERADCOM Qualification

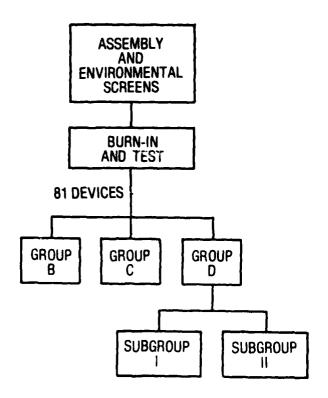


Figure 10-2. TAB Qualification Schedule

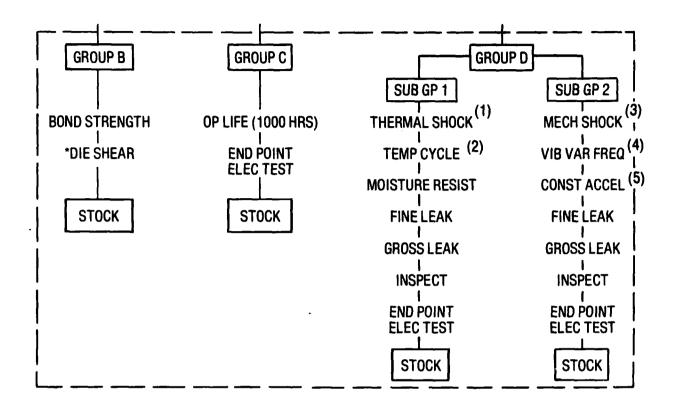


Figure 10-3. ERADCOM/Honeywell Qualification Tests

All tests in accordance with MIL-STD-883

- (1) Method 1011 Cond B 15 cycles min
- (2) Method 1010 Cond C 100 cycles min
- (3) Method 2002 Cond C (min) Y, orientation only (3000 g's peak, 0.3 msec pulse)
- (4) Method 2007 Cond A (20 g's peak)
- (5) Method 2001 Cond A (5000 g's, Y_1 orientation only)

COSTS

Honeywell has performed analysis of the manufacturing costs associated with TAB technology. This analysis basically consists of three different items, each one of which was addressed and reviewed separately:

- a. A theoretical cost model*, which was generated on the basis of two hypothetical standard hybrid modules, one of low and one of high complexity.
- b. Breakout of labor by task and grade employed during the build of 1604 Hybrid Sync Counter circuits, in complexity somewhat similar to andard hybrid module number 1 of the cost module.
- c. Projected production costs of Sync Counter Hybrids build with TAB in quantities of 100, 1000, 5000 and 10,000 as compared to build with chip and wire (C&W) techniques.

Each one of the above elements will be briefly discussed below.

A. Cost Model

The purpose of the cost model was to analyze the production costs of hardware utilizing either conventional chip and wire (C&W) technology or Tape Automated Bonding.

The models prepared to predict production costs are based on two hypothetical hybrids of different complexity. Table 11-1 shows the makeup of standard hybrid modules I and II. Of interest is the break-even quantity of hybrids with wirebonding versus hybrids built with TAB. For Standard Module Number I this quantity is approximately 900 circuits, for Standard Module Number II approximately 200 circuits. These quantities are lower than anticipated on the basis of the nonrecurring costs, and are greatly influenced by the first electrical test yield.

Figure 11-1 shows a graph depicting the comparative cost analysis of Standard Module Number 1, Figure 11-2 shows this graph for Standard Module Number 2. Appendix III at the back of this report includes the entire cost model.

*Cost model developed under Contract DAAK40-76-C-1079.

B. Labor Employed by Task and Grade During the Build of the E/M Sync Counter

Nine labor categories were utilized in the build of the E/M Sync Counter circuit and the hours are broken out by task. Two engineering, three technician and four assembly labor grades were employed. The breakout of hours is shown in Table 11-2.

A total of 3459 hours, of which 533 for nonrecurring tasks, were expended in the fabrication of the 1604 circuits. The remaining 2920 hours of recurring labor provide an average of 1.82 hours expended on each of the 1604 circuits fabricated. The actual hours and those calculated in the Projected Production Costs (1.82 vs 1.88) correspond very closely and show the relative accuracy of the cost model.

C. Projected Production Costs

LABOR

A 1980 production quote for Sync Counters was used as the base for the C&W estimate. Hours were costed at an assembly labor grade. Material and support were held to the relative cost ratios of these items to assembly cost that occurred in the original production quote. This gives a recurring labor per unit of \$47.79, material per unit of \$34.82 and support per unit of \$100.00.

TAB hours were derived from process deltas to the original production quote. The areas of difference are component mount and wirebond plus inspection. Component mount was factored to 25 percent of the production effort based on a linear reduction of the effort based on one cap to mount versus one cap and three chips in chip and wire. Operation of chip separation; inner and out lead bonding, chip test, and framing based on the standards in the cost model using an EHR* of 3.0. Wirebond and inspection were limited to the manually wirebonded wires remaining in the TAB build. Overall yields through first test for C&W (52 percent) and TAB (86 percent) show a 65.4 percent improvement for TAB that was used to factor down troubleshoot and rework hours. The hours per unit show a 48 percent reduction to 1.88 hours per unit. This delta was reviewed with the Program Manager for reasonability.

MATERIAL

The material deltas were based on actual TAB material for those items primarily lead frames.

*EHR (Earned Hour Ratio) - The actual time required for performance of a task compared to a standard time derived from time and motion studies for that same task.

NONRECURRING

Nonrecurring costs are based on the cost model with a review through the Program Manager for continued cost reasonability. Lead frames design masks, IC test programs and fixturing and thermodes are the primary nonrecurring deltas.

Figure 11-3 shows the curves for production cost savings of the E/M Sync Counter built with TAB versus chip and wire. Note the crossover point at 776 devices.

Table 11-3 shows estimated costs for new production with TAB and C&W for the E/M Sync Counter in quantities of 100, 1000, 5000 and 10,000 devices.

Table 11-1. Standard Module Configurations Used in Cost Model

Configuration	<u>No. 1</u>	<u>No. 2</u>
Substrates	1	1
Layers	6	8
Size	1×1 inch	2 x 2 inches
IC Types	3	11
No. ICs	7	32
No. IC Wires	126	359
Projected Loss	10%/2.5%	15%/2.5%
(C&W/TAB)		
Resistor Chip Types	2	7
No. Resistor Chips	4	20
No. Resistor Wires	72	225
	3	9
Capacitor Types	8	24
No. Capacitors		6
Modules/Burn-In Board	21	U

Table 11-2. Analysis of Labor Requirements for TAB Sync Counter Fabrication by Task and Grade

	Engin	eer	Tec	hnici	an		Assem	bly	
	I	II	I	II	III	I	II	III	IV
E/M Synchronous Counter Relayout	20	25	10	130	98				
Lead Frame and Bump Mask Design	20		40	118	128				
Plate Tape Mount and Dice Wafers	30	50	280	30	2	54	115	46	20
Substrate Fabrication (Thick Film)	12			76	63		1		
*ILB, OLB and Assembly Operations	50	18	280	243	155	541	48	5	
Circuit Electrical Test	50	64		26		20	212		
Chips-On-Tape, Burn-In	20	22	48	30	60				
Circuit Burn-In	10	40	40	84	25				
Total, by Labor Grade	212	219	698	737	531	615	376	51	20

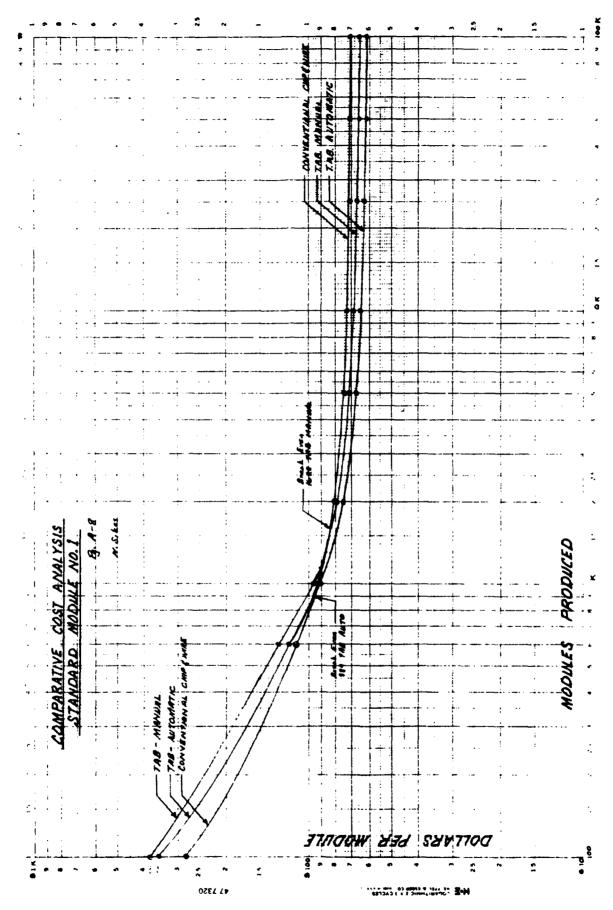
^{*}This task includes all visual inspections, testing of chips-on-tape, package seal and leak test operations.

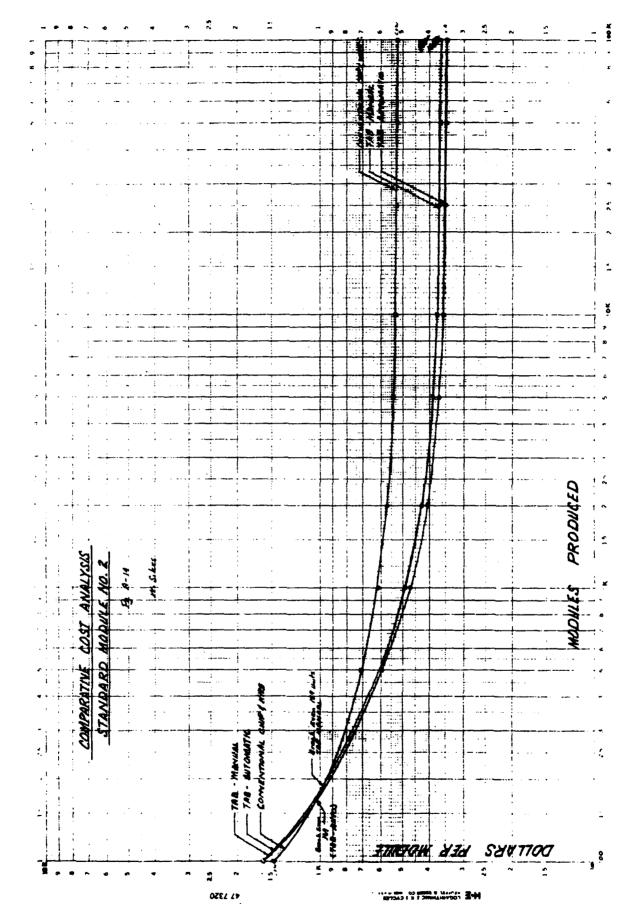
- Note 1. Total circuits fabricated 1604
- Note 2. Tasks 1 and 2 involve nonrecurring labor; tasks 3-7 only involve recurring labor
- Note 3. In all labor categories, the highest skill labor grades are represented by Roman Numeral I and lowest skill by Roman Numeral IV.

TAble 11-3. Actual Cost - E/M Sync Counter Circuits

(Chip and Wire Versus TAB Process)

Unit Quantity	C&W Unit Cost \$	TAB Unit Cost \$	C&W Total Cost K\$	TAB Total Cost K\$	TAB Savings K\$
100	272.61	323.14	27.3	32.3	~5
1,000	194.21	189.93	194.2	189.9	4.3
5,000	184.41	178.09	922.1	890.5	31.5
10,000	183.51	176.61	1835.1	1766.1	69





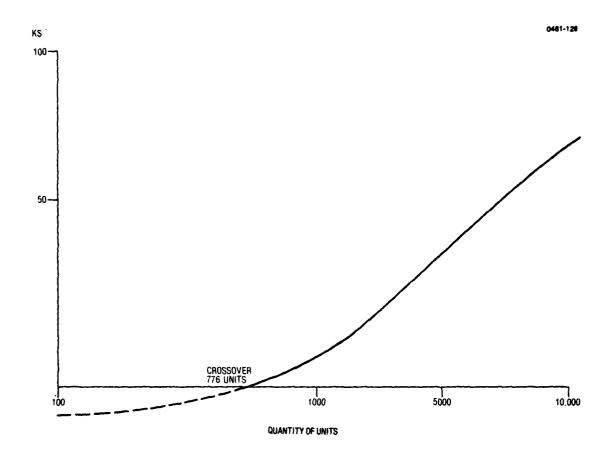


Figure 11-3. Cost Savings of TAB

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Section 12

CONCLUSIONS

On the basis of the results of this MM&T project, Honeywell believes that TAB is a viable and successful technology. Its application will be governed by factors related to circuit design, complexity, production volume, and the final use environment.

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- "Wafer Bumping for Tape Automated Bonding", James M. Montante, William R. Rodrigues de Miranda, and Dr. Rudolph G. Oswald, International Microelectronics Symposium of ISHM, Baltimore, MD, October 1977.
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Appendix 1
FAILURE ANALYSIS REPORT

ANALYTICAL SERVICES LAB WORK REQUEST

REQUEST	NUMBER - CODE	
66-F		

Honeywell

PART NUMBER 34032548 PART NAME/FUNCTION SYNC Counter

12001 STATE HIGHWAY 55, PLYMOUTH, MINNESOTA, 55441, TELEPHONE 612/541-2508, 2442

	REQUESTER	PHONE	DIVISION DEPARTMENT
	Will Perry	HVN 463-3856	AvD - Florida Hybrid
	REQUEST DATE CHARGE NUMBER	TECHNOLOGY	<u> </u>
	1/23/81 SD545-1000	Hybrid/Lo	W Power Schottky T ² L
		7 FAILURE	SEM - If Needed X ELEC. TEST
		MATERIALS	□ EDS □ ELEC. PROBE
	☐ ENGINEERING ☐ OTHER	LINE QUALITY	☐ AUGER 🖾 OPTICAL/PHOTO
		CALIBRATION	CROSS-SECTION OTHER
		OTHER	
			
		DEVICE HISTORY	
1	APPROXIMATE HOURS TO FAIL	URE OPERATION ENVIRON	MENT (TEMP) OPERATION ENVIRONMENT (HUM)
_	X FAILURE 0	As Indicate	n/A
REQUESTER	OTHER		
JES	COMMENTS		
8	4 failed dynamic ATP test at temp (S +100°C, all "CBI" Lot).	/N 1/52 - Minus 55 ⁰	C; S/N 1791, 1810 & 1818 at
2	1 chip & wire (S/N 0110) failed 100°	C test - nre B I	
	1 TAB S/N 1029 first test room tempe	rature.	
	WORK REQUESTED (DETAIL)		
	,		
	Check U_2 for anomalies - Devices hav	e been delidded. F	ind cause of failures.
	RESULTS (SUMMARY) S/N 1810 and 1818 were found to have	contamination in t	ho nitrido C/N 1701 oubibited
	contamination in a metal contact are	a.	ne intride. 3/N 1/31 exilibited
	S/N 1029's U ₂ chip was incorrectly b	onded.	
	S/N 1752 and 0110 contained die diff	usion faults.	
	With exception of S/N 1029, these fa	ilures were caused	by processing defects. manifested
ANALYST	at first electrical test.		, , , , , , , , , , , , , , , , , , ,
Z			
<			
			CORRECTIVE ACTION SHEET ATTACHED
			YES NO
	/) A (MP. DATE DISTRIBUTION	APPROVAL 3/ //
	Know Coche 2/14	1/3/'	John Militarda 413/8/
HA-3	42	Δ1-2	:

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PROCEDURE

R. Nelson/C. Goerke

Optically examine for visible contamination and photograph anomalies. Gold coat suspect devices before SEM analysis. SEM photographs of anomalies. Etch nitride using the LFE Plasma Asher Etcher. Optically examine for anomalies after etch, photograph. Curve tracer analysis.

EQUIPMENT USED

Zeiss Universal Optical Microscope
Denton Vacuum Sputter Coater - (Gold Coat Samples)
SEM - Scanning Electron Microscope - JSM T-200
LFE Plasma Asher Etcher
Tektronix 576 Curve Tracer

ANALYSIS

Device #1810 - Contamination was observed under optical analysis (Figure 1 & 2). Device was etched in the LFE Asher Etcher to remove the nitride. After nitride was removed, the contamination present in Figure 2 was gone (Figures 3 & 4). Analysis was discontinued at this point on this device.

<u>Device #1818</u> - Contamination was observed under optical examination (Figure 5 & 6). The nitride contamination is similar to that found in Device 1810. Curve tracer analysis on this device revealed no failures. This contamination could have contributed to the device failing to meet specifications at high temperature.

<u>Device #1791</u> - Optical examination revealed metal contamination (Figures 7 & 8) that could, when subjected to temperature changes cause failure of the device to meet specifications. After nitride removal (Figures 9 & 19), the contamination in the metal remained. SEM analysis (Figures 11-16) indicates that this contamination is on and around the metal.

Device #1752 - Optical examination (Figures 17 & 18) revealed a processing defect possibly diffusion related. SEM analysis was performed (Figures 19-22) and indicated that the defect was below 2nd metal. The anomaly extended between to metal areas which under temperature conditions could possibly become conductive.

Device #0110 - Optical examination (Figures 23-26) indicates that there are diffusion faults present. These faults appears to occur between metal areas and below the nitride. Area indicated in Figures 24 are just two of the many possible anomalies present that could cause the failure when subjected to temperature changes.

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Device #1029 - Optical analysis (Figure 27) revealed no visible contamination that could cause a failure. Curve tracer analysis on this device indicated a short from Pin 11 to ground on Pin 16. Continued optical examination indicated the failure to be that U_2 (Figure 28) was bonded incorrectly.

CONCLUSION

Two devices (S/N 1810 & 1818) were found to have contamination imbedded in the nitride. One device (S/N 1791) was found to have metal contamination which under the temperature conditions may have caused the failures. Two devices (S/N 1752 and 0110) exhibited what appears to be diffusion faults in areas between metal runs. These faults could cause the devices to fail to meet specifications under the high temperature test conditions. One sample (S/N 1029) contained incorrectly bonded wires from U2 to the bond pads, apparently made when replacing the tabbed chip. These wires connected the output on Pin 11 to the ground pin, and thus caused the failure.

With exception of S/N 1029, the failures were all caused due to processing defects in the chip fabrication cycle and would have been detected before assembly if the chip had seen high temperature testing prior to assembly.

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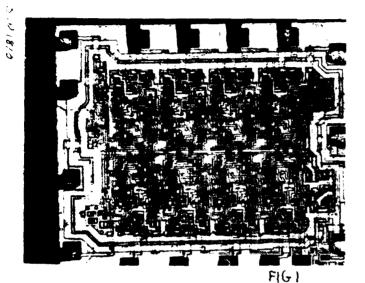
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Figure 1. Sample 1810 Overall view at 25% of U₂. Curve tracer analysis on this device revealed no defects at room temp.

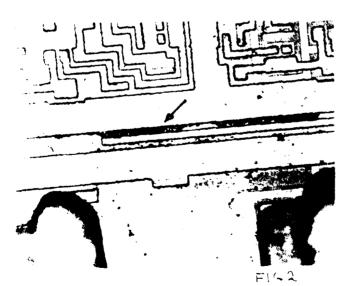


Figure 2. Sample 1810 Optical photo at 261X of contamination.

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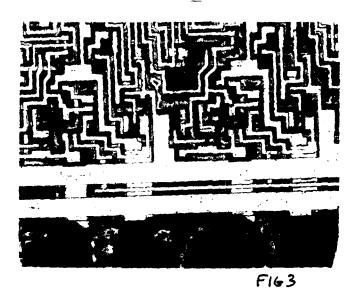


Figure 3. Sample 1810 162X optical photo after nitride has been removed. Contamination that was present in Figure 2 is now eliminated.

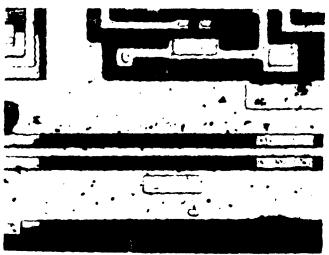


Figure 4. Sample 1810
437X optical photo after
nitride removal. Contamination
that was present in Figure 2
is now gone. Unable to
determine exact cause of
failure in this device.

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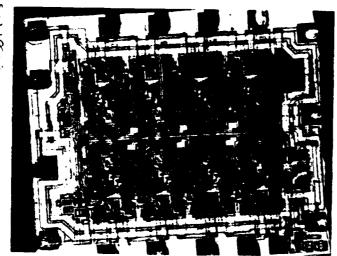
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Figure 5. Sample 1818 45X optical photo overall view of U2. Curve tracer analysis on this device indicated no failure at room temperature.

Figure 6. Sample 1818 261X optical photo of contamination imbedded in the nitride. A similar type contamination is in Figure

2, Sample 1810.

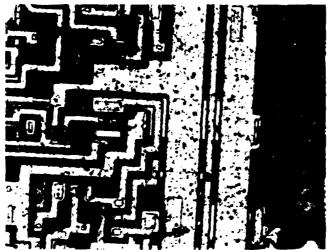


FIG 6

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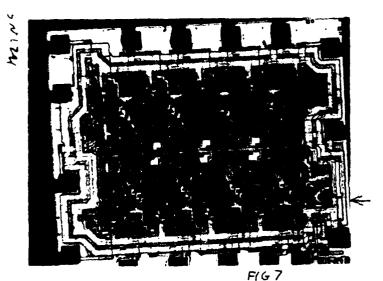
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Figure 7. Sample 1791 45X optical view of $\rm U_2$. Contamination site in the circled area.

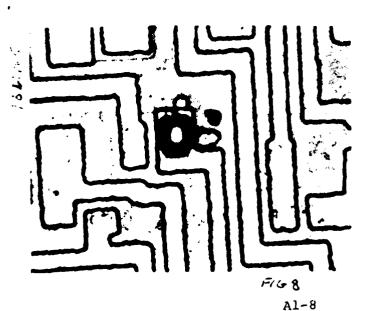


Figure 8. Sample 1791 707X optical photo of metal contamination in the circled area in Figure 7.

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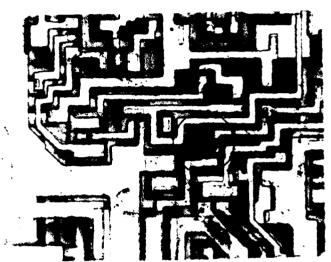


Figure 9. Sample 1791 162X optical photo taken after asher etch of the nitride. Metal contamination remained. Same area as Figure 8.



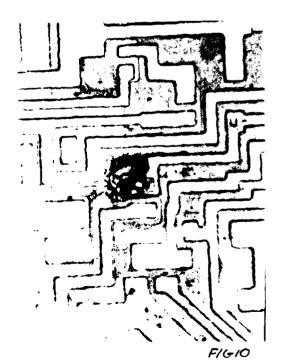


Figure 10. Sample 1791 437X optical photo taken after asher etch of nitride with metal contamination remaining. Same area as in Figure 8.

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Figure 11. Sample 1791 2000X 45° tilt SEM photo of metal contamination in Figure 8.



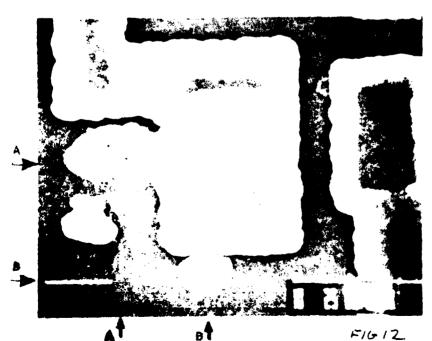


Figure 12. Sample 1791 2000X 00 tilt SEM photo of metal contamination. Same area as Figure 11.

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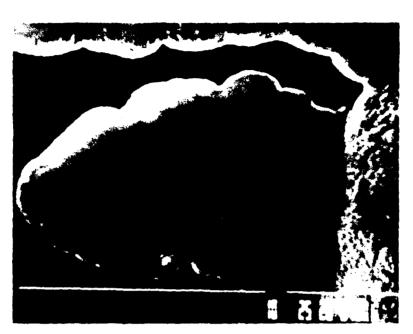


Figure 13. Sample 1791 7500X 0⁰ tilt close-up SEM photo of area A-A in Figure 12. All SEM photos taken before nitride removal.

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Figure 14. Sample 1791 7500X 45° tilt SEM photo of same area as Figure 13.

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Figure 15. Sample 1791 10,000X 45° tilt SEM photo of the area in Figure 13.





Figure 16. Sample 1791 7500X 45° tilt SEM photo of Area B-B in Figure 12.

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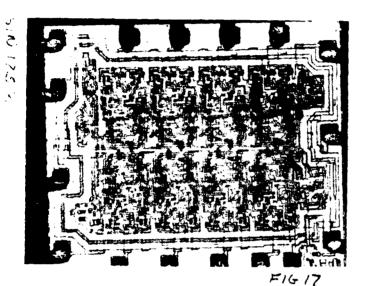


Figure 17. Sample 1752 45% optical photo of U_2 .

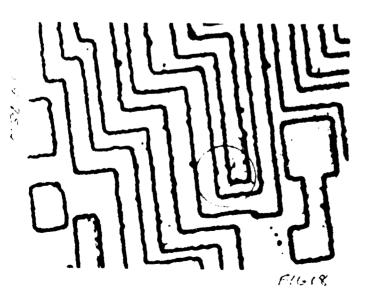


Figure 18. Sample 1752 141X optical photo of possible failure causing processing defect.

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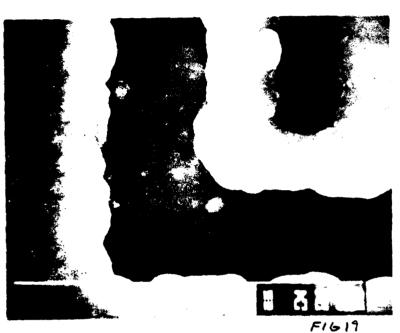


Figure 19. Sample 1752 5000X 0 tilt SEM photo of processing defect in Figure 18.



Figure 20. Sample 1752 7500X 45⁰ tilt SEM photo of processing defect in Figure 19. Possible failure causing anomalie.

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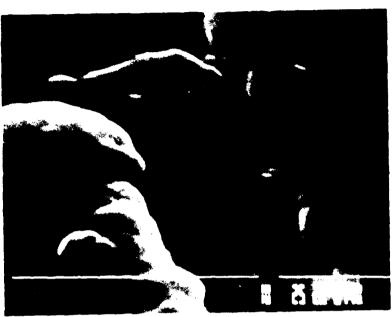


Figure 21. Sample 1752 $7500 \times 40^{\circ}$ tilt SEM photo of processing defect in Figure 20.

FIG 21

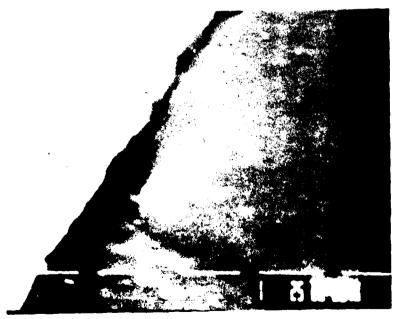


Figure 22. Sample 1752 20,000X 40° tilt SEM photo of processing defect in Figure 21.

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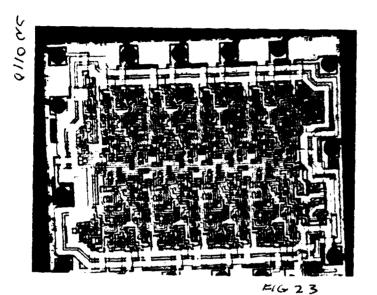


Figure 23. Sample 0110 45% optical overall view of $\rm U_2$.

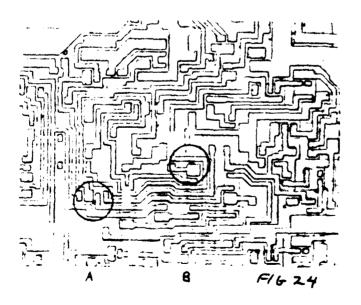


Figure 24. Sample 0110. 162X optical photo of possible failure causing diffusion faults. Anomalies appear to occur below the oxide and nitride.

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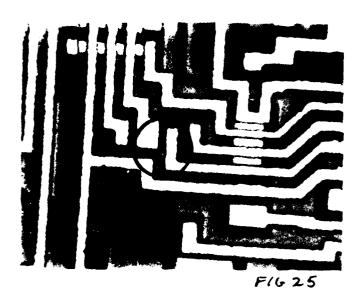


Figure 25. Sample 0110 437X optical photo of possible failure causing diffusion faults. Area A of Figure 24.

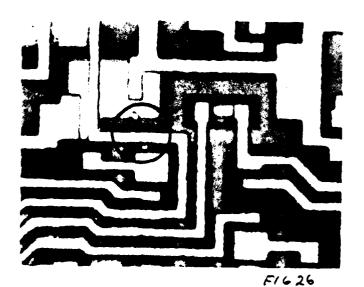


Figure 26. Sample 0110 437X optical photo of possible failure causing diffusion faults. Area B in Figure 24.

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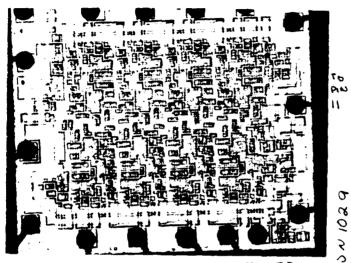
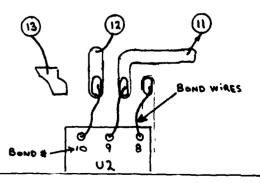


Figure 27. Sample 1029 Overall view of 45X of U₂. No contamination visible.





Figure 28. Sample 1029
29X optical photo of failure
mode. Three bond wires are
shifted over and bonded to the
wrong area. Pin 11 bond wire
should be on the center bond
bump in this Figure. Curve
tracer analysis indicated
a short to ground on Pin 11.
Bond wire that is connected
to Pin 13 should be on Pin 12.



A1-18

Appendix II
ANALYSIS REPORT, NO. V02907



PRODUCT ASSURANCE

PAGE OF

LABORATORY

ANALYSIS NO. V02907

HONEYWELL **Avionics Division** St.Petersburg FL

ANALYSIS REPORT

DATE ISSUED 21 JANUARY 1981

PART NAME AND DESCRIPTION VENDOR NAME REQUESTER

LOT/AR/ST

E/M SYNC. COUNTER HONEYWELL

D. WRIGHT

PROGRAM NAME FART NUMBER 4873 34032548

VENDOR PART NUMBER

. DATE CODE 0423

1

CONCLUSIONS:

NO DIE/MOUNT CONTAMINATION DETECTABLE - EPOXY THIN & POROUS

REASON FOR ANALYSIS

TWO OF THE THREE PACKAGE DICE FAILED DIE SHEAR TEST. DETERMINE CAUSE.

RESULTS

A SEM/EDS ANALYSIS OF THE MATING EPOXY AND DIE SURFACES SHOWED NO DETECTABLE CONTAMINATION. THE EPOXY SURFACE UNDER THE FAILED DICE WAS FOUND TO BE MORE PORQUEZ/VOIDED THAN UNDER THE NON-FAILURE. SEE FIGURE 1. THIS MAY HAVE PROVIDED A REDUCED BOND SURFACE AREA WHICH CONTRIBUTED TO THE FAILURE.

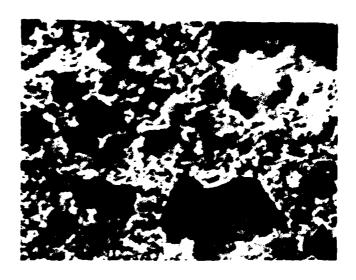
IT IS RECOMMENDED THAT FURTHER CONTAMINATION IDENTIFICATION TECHNIQUES BE PURCUED, PARTICULARLY IN THE ORGANIC SPECTRA.

T(E) WH100 47

PREPARED BY

A2-2

DATE



FAILED EPOXY SURFACE (~500X)



NON-FAILED EPOXY SURFACE (~500X)

FIGURE 1 SEM VIEWS OF EPOXY MOUNT SURFACES

Appendix III
COST MODEL

TAPE AUTOMATED BONDING

vs.

CONVENTIONAL CHIP & WIRE

COST MODEL

CONTENTS

	PAGES
INTRODUCTION	A3-4
RECURRING PROCESS COSTS	A3-6
NON-RECURRING COSTS	A3-10
MATERIAL COSTS	A3-11
REWORK	A 3-12
ADDENDIX	A 3-14

INTRODUCTION

The following is a cost model intended for use in calculating production costs of hardware utilizing either conventional chip and wire technology or tape automated bonding. The model is organized as follows:

Section I

This section displays 23 Recurring Process Cost Formulas which may be used in combinations to calculate the recurring assembly costs of any module. The formulas are broken into two major sections: "Conventional Processes" and "T.A.B. Processes". They are designated with the prefix letters "C" or "T", respectively. (A3-6 - A3-9)

Section II

This section displays 9 Non-Recurring Cost Formulas which may be used in combinations to calculate the non-recurring assembly costs of any module. These formulas are designated with the prefix letters "NR". (A3-10)

Section III

This section displays 11 Material Cost Formulas which may be used in combinations to calculate the material costs of any module. These formulas are designated with the prefix letter "M". (A3-11)

Section IV

Page A3-12 displays the statistical relationship between individual I.C. chip yields and overall package yields varying with the number of I.C. chips per package. This information is utilized in the following Recurring Process Cost Formulas:

Process No.	Process			
C-8	Troubleshoot			
C-9	Rework			
C-10	Re Burn-in			
C-11	Re Package Test			
T - 7	Rework			

Page A3-13 displays the relationship between I.C. chips per module and troubleshoot hours per module. This information is utilized in Recurring Process Cost Formula C-8, Troubleshoot.

Appendix

The remaining pages contain two examples of application of the cost model.

Page A3-14 displays configuration information for two "standard modules". All of the information shown on this page is necessary for full application of the cost model.

Page A3-15 displays both the IC and Package Failure Rates associated with each of the two "standard modules". Calculations shown on this page are based on information contained in Section IV-1.

Pages A3-16 through A3-21 contain the application of the cost model to Standard Module No. 1. The model has been utilized to project costs for three methods:

- 1. Conventional Chip and Wire
- 2. T.A.B. utilizing automatic equipment
- 3. T.A.B. utilizing manual equipment

Page A3-22 displays the average cost of Standard Module No. 1 for volumes between 1 and 100K.

Page A3-23 displays the average cost information in graphical form as well as the breakeven points for the three processes.

Pages A3-24 through A3-29 display the same cost information for Standard Module No. 2.

RECURRING LABOR COSTS - CONVENTIONAL PROCESSES

COST	te .0012 hrs/substrate ire .0019 hrs/print .0014 hrs/print x PDF)+(.0014 x PD's)	.0023 hrs/comp. type .0039 hrs/chip .0008 hrs/mod. type)+(.0039 x # chips)]		.0050 hrs/substrate .0009 hrs/point .0001 hrs/component .00046 hrs/wire points)+(.0001 x # comp.) +	.0006 hrs/chip .0004 hrs/wire .0140 hrs/chip % .0007 hrs/wire 1 x # wires)
PROCESS	o Clean Substrate o Print, Dry, Fire o Print, Dry Cost Formula: \$17.95 (.0012 +(.0019 x PDF)+(.	o Unload substrate, position new one .0023 o Load Chip o Cure Cost Formula: \$17.95 C.0008 +(.0023 x # types)+(.0039	o Same as C-2 above.	o Unload substrate, position new one o Align reference points o Initiate automatic mode o Bond wire Cost Formula: \$17.95 (.00046 x # wires))	o Inspect for component position & damage o Inspect wire bonds o Remove & replace comps. • .20 hrs/IC x 7% replacement o Remove & replace wire • .0045 hrs/wire x 15% Cost Formula: \$17.95 \$(.0146 x # chips)+(.0011
EQUIPMENT	Presco Printer/Dryer Tempress Lindberg Furn.	Laurier Epoxy Bonder	Laurier Epoxy Bonder	K&S Automatic Bonder	K&S Manual Bonder
PROCESS	Thick Film Printing	Component Mount	Capacitor Mount	Wire Bonding	Visual Inspect G Rework
PROCESS NO.	C-1	C-2	C-3	C-4	C- 5

RECURRING LABOR COSTS - CONVENTIONAL PROCESSES (cont'd)

PROCESS COST	o Load module to burn-in board o Monitor burn-in .5 hrs/day x 7 days = 3.5 hrs/B.I. Board o Unload modules from burn-in board Cost Formula: \$17.95 ((3.5 * modules/board) + .0048)	Cost Formula: $$17.95 \times .02 \text{ hrs/module} = 0.36	Cost Formula: \$17.95 x T.S. hrs/pkg. x # failed packages	o Remove and replace component, wirebond .0320 hr/failed comp. Cost Formula: \$17.95 x .2000 x # failed Comps/module	Cost Formula: Initial B.I. cost x # failed packages.	Cost Formula: Initial test cost x # failed packages.	Cost Formula: \$17.95 x .016 hrs/pkg = \$0.29
EQUIPMENT	Burn-in oven	Automatic Test Station		K§S Manual Bonder	Burn-in Oven	Automatic Test Station	SSEC Pkg. Sealer
PROCESS	Burn-in	Package Test	Troubleshoot	Rework	Re Burn-in	Re Package Test	Seal Package
PROCESS NO.	9-0	C-7	C-8	ი ე A3−7	C-10	C-11	C-12

RECURRING LABOR COSTS - T.A.B. PROCESSES

₽I	.0830 hrs/wafer .0396 hrs/wafer 2.0000 hrs/wafer .0500 hrs/wafer .5000 hrs/wafer .5000 hrs/wafer	er = .0027 hrs/IC .0027 hrs/chip x	.0010 hr/IC	.0200 hr/IC .0200 hrs/IC x	.0028 hr/IC .0028 hrs/IC x	.0083 hr/IC .0083 hrs/chip x	.0003 hr/IC .0003 hrs/IC x	.0028 hrs/IC .0028 hrs/IC x
PROCESS COST	o Clean Wafer o Position wafer in holder o Saw o Fracture Scribe Lines o Place IC in waffle pack	2.6726÷1000 IC's/wafer = .0027 hrs/IC Cost Formula: \$17.95 x .0027 hrs/chip x # of chips/module	o Bond IC to lead frame Cost Formula: \$17.95 x # IC's/module	o Bond IC to lead frame Cost Formula: \$17.95 x # IC's/module	o Test IC in lead frame Cost Formula: \$17.95 x # IC/module	o Test IC in lead frame Cost Formula: \$17.95 x # IC/module	o Cut lead frame Cost Formula: \$17.95 x # IC/module	o Cut lead frame Cost Formula: \$17.95 x # IC/module
EQUIPMENT	Dicing Saw		1/L Bonder 11000	I/L Bonder Mark IV	Automatic Test Station	Manual Test Station	Automatic Framing Machine	Manual Framing Machine
PROCESS	Chip Separation		Inner Lead Bonding (Automatic)	Inner Lead Bonding (Manual)	Chip Test (Automatic)	Chip Test (Manual)	Framing (Automatic)	Framing (Manual)
PROCESS NO.	T-1		T-2-A	T-2-T	T-3-A	T-3-M	T-4-A	T-4-M

RECURRING LABOR COSTS - T.A.B. PROCESSES (cont'd)

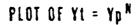
PROCESS COST	o Bond IC to substrate .0020 hrs/IC Cost Formula: \$17.95 x .0020 hrs/IC x # IC's/module	o Bond IC to substrate .0083 hrs/IC Cost Formula: \$17.95 x .0083 hrs/IC x # IC's/module	o Inspect for component .0006 hrs/IC position & damage o Inspect outer lead .0003 hrs/bond bonds o Remove & replace IC's .2000 hrs/IC x 7% replacement = .0140 hrs/IC Cost Formula: \$17.95 ((.0146 x # IC's) + (.0003 x # 0/L bonds))	o Remove and replace IC .2000 hrs/IC Cost Formula: \$17.95 x .2000 x # failed IC's/module
EQU I PMENT	0/L Bonder #4821	0/L Bonder #4810	Manual O/L Bonder	Manual O/L Bonder
PROCESS	Outer Lead Bonding (Automatic)	Outer Lead Bonding (Manual)	Visual Inspect G Rework	Rework
PROCESS NO.	T-5-A	T-5-M	T-6	T-7

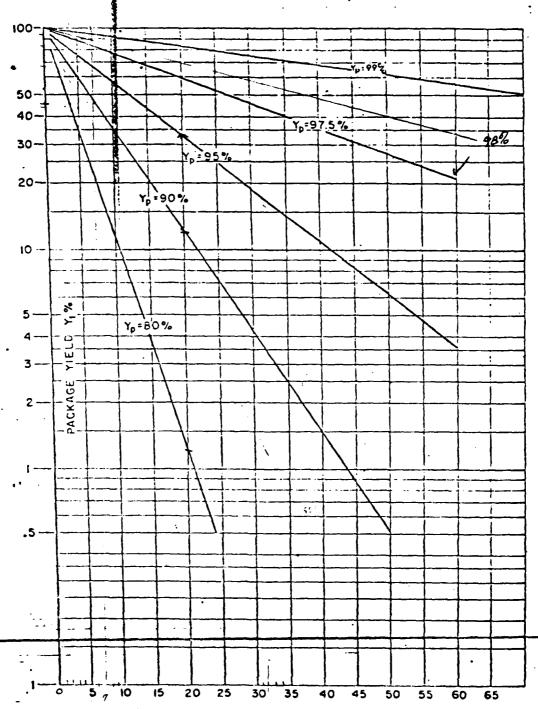
NON-RECURRING COSTS

ITEM NUMBER	ITEM		COST FORMULA	V.
NR-1	Thick Film Screens	₩	15.00/layer	/er
NR-2	Program Automatic Wirebonder	₩	0.15/wire	je Je
NR-3	Lead Frame/Mask Design (TAB only)	€ \$	500.00/IC type	type
NR-4	Masks (2) (TAB only)	₩	720.00/IC type	type
NR - 5	Thermode (TAB only)	6/3	295.00/IC type	type
NR-6	Test Cabling (TAB only)	6/3	50.00/IC type	type
NR-7	I.C. Test Program (TAB only)	€9	950.00/IC type	type
NR-8	I.C. Test Fixturing (TAB only)	€43	215.00/IC type	type
NR-9	Package Level Testing, Programs, Fixturing	\$3	\$3,000.00/IC	

ATERIAL COST

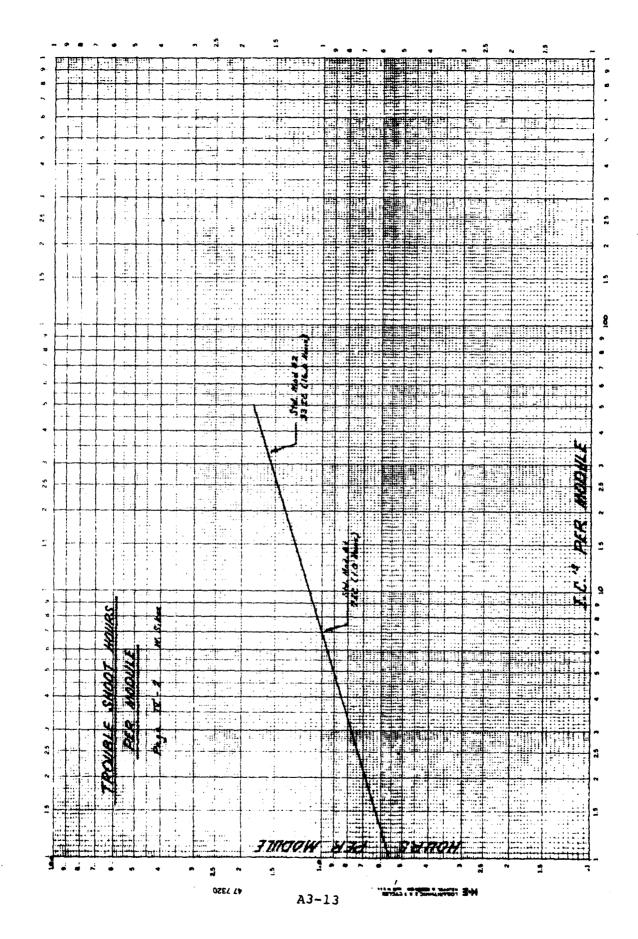
MATERIAL NUMBER	MATERIAL	COST FORMULA
M-1	Substrate 1" x 1"	\$0.50/substrate
M-2	Substrate 2" x 2"	<pre>\$0.75/substrate</pre>
M-3	Integrated Circuits	\$1.00/I.C.
M-4	Integrated Circuits with Bumps	\$1.10/I.C.
M-5	Lead Frame	\$0.70/I.C.
M-6	Resistor Chip	\$1.00/Resistor Chip
M-7	Capacitor	\$1.00/Capacitor
Ж-8	Gold Wire	\$0.01/Wire Bond
6-M	Thick Film Inks	\$0.90/Print
M-10	Package	\$9.75/Package
M-11	Lid	\$3.75/Lid





NUMBER OF IC DICE PER PACKAGE, N

Figure 1



STANDARD MODULE CONFIGURATION

Substrates	1	1
Layers	6	8
Size	1" x 1"	2" x 2"
I.C. Types	3	11
No. IC's	7	32
No. IC Wires	126	359
Projected Loss (C&W/TAB)	10%/2.5%	15%/2.5%
Resistor Chip Types	2	7
No. Resistor Chips	4	20
No. Resistor Wires	72	225
	3	9
Capacitor Types		
No. Capacitors	8	24
Modules/Burn-in Board	21	6

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							}						
	STOCKED	.83	.16	0	1.0			. 45	. 54	.01	1.00		
	NO.(1) FAILED PKGS	.17	.01	0	.18			.55	.01	00.	.56		
T.A.B.	NO. FAILED IC'S	.175	.004	0	.18			800	.020	000	.820		
	TEST NO.	-	2	ĸ				r-4	7	ŧ٠			
	CHIP FAILURE RATE	2.5%						2.5%					
	STOCKED PKGS	.47	. 48	.04	.01	1.00			.84	.13	.01	10.	1.00
	NO.(1) FAILED SPKGS	.53	.05	.01	90	.59		66.	.15	. 02	.01	00.	1.17
CHIP 6 WIRE	NO. FAILED	. 700	.070	. 007	000	. 78		4.800	.720	.108	.016	000	5.644
Ö	TEST NO.	~	2	89	4			-	2	3	4	Ŋ	
	CHIP FAILURE RATE	10\$				→		15%				>	
	NO. IC's/ PKG.	7						32					
	STD. MOD. NO.	-						7					

A3~15

(1) Ref. Plot of Yt = Yp^N

STANDARD MODULE NO. 1 - CONVENTIONAL CHIP & WIRE

RECURRING LABOR COSTS:

PROCESS	PROCESS NUMBER	COST FORMULA	COST PER MODULE
Thick Film Printing Component Mount	C-1 C-2	\$17.95 (.0012 +(.0019 x 4)+(.0014 x 2)) \$17.95 (.0008 +(.0023 x 5)+(.0039 x 11)	\$ 0.21 0.99
Capacitor Mount	C-3	C.0008 + (.0023 x 3) + (.0039 x	0.70
Visual Inspect 6 Rework	C-5	((.0146 x 11)+(.0011 x 198)	6.79
Burn-in	9-)	\$17.95 ((3.5 ÷ 21) + .0048)	3.08
Package Test	C-7	\$17.95 x .02	0.36
Troubleshoot	ထ င် - ပ	\$17.95 x 1.0 x .59	10.59
Rework Re Burn-in	C-3	\$1.95 X .2000 X ./8 \$3.08 X .59	1.82
Re Package Test	C-11	\$0.36 x .59	0.21
Seal Package	C-12	\$17.95 x .016	0.29
		TOTAL RECURRING COST =	\$29.97
NON-RECURRING COSTS:			
ITEM	I TEM NUMBER	COST FORMULA	TOTAL NON- RECURRING
Thick Film Screens	NK-1	\$15.00/layer x 6 layers	90.00
Frogram Auto Wirebonder	NR-2	\$0.15/wire x 198 wires	30.00
rky. Level lest, Progs., Fixt.	NR-9	\$3000/IC x 7 IC's	\$21,00.00
		TOTAL NON-RECURRING = \$	\$21,120.00

STANDARD MODULE NO. 1 - CONVENTIONAL CHIP & WIRE (cont'd)

MATERIAL COSTS:

MATERIAL COSTS	7.00 4.00 8.00 1.98 5.40 9.75	\$40.38
COST FORMULA	<pre>\$0.50/sub. x 1 sub./module \$1.00/IC x 7 IC/mod \$1.00/chip x 4 chips/mod \$1.00/cap x 8 caps/mod \$0.01/wire x 198 wires \$0.90/print x 6 layers \$9.75 x 1 pkg/module \$3.75 x 1 pkg/module</pre>	TOTAL MATERIAL COST =
MATER I AL NUMBER	M-1 M-3 M-5 M-7 M-8 M-9 M-10	
MATERIAL	Substrate 1" x 1" Integrated Circuit Resistor Chip Capacitor Gold Wire Thick Film Inks	p r q

TOTAL MATERIAL COST =

STANDARD MODULE NO. 1 - AUTOMATIC T.A.B. PROCESSES

TOTAL RECURRING COST =

STANDARD MODULE NO. 1 - AUTOMATIC T.A.B. PROCESSES

(cont'd)

TOTAL	NON RECURRING	\$ 90 11 1500 2160 885 150 2850 645	\$29,291
(cont'd)	COST FORMULA	\$15.00/Layer x 6 Layers \$ 0.15/wire x 72 wires \$ 500/IC Type x 3 IC Types \$720/IC Type x 3 \$295 x 3 \$50 x 3 \$215 x 3	\$3000/IC × 7 IC TOTAL NON-RECURRING
	I TEM NO.	NR-1 NR-2 NR-3 NR-4 NR-5 NR-6 NR-7	NR-9
	ITEM	Thick Film Screens Program Auto. Wirebonder Lead Frame/Mask Design Masks Thermode Test Cabling IC Test Program IC Test Fixturing	Pkg. Level Testing, Progs, Fixt.

STANDARD MODULE NO. 1 - AUTOMATIC T.A.B. PROCESSES

MATERIAL COSTS:

MATERIAL	\$ 0.50	4.00	4.90	8.00	. 72	5.40	9.75	3.75
COST FORMULA	<pre>\$0.50/sub x 1 sub/Module</pre>	1.00/chip x 4 chips/module 1.10/IC x TIC/Module	0,70/IC x TIC/Module	1.00/cap x 8 caps/Module	0.01/wire x 72 wires/Module	0.90/Print x 6 Prints	9.75/Pkg x 1 Pkg/Module	$3.75/\text{Lid} \times 1 \text{Lid/Module}$
MATERIAL NO.	M-1	M-6 M-4	M-5	M-7	M 1 8	6-M	M-10	M-11
MATERIAL	Substrate 1" x 1"	Resistor Chip Integrated Circuits with	bounts lead frame	Capacitor	Gold Wire	Thick Film Inks	Package	Lid

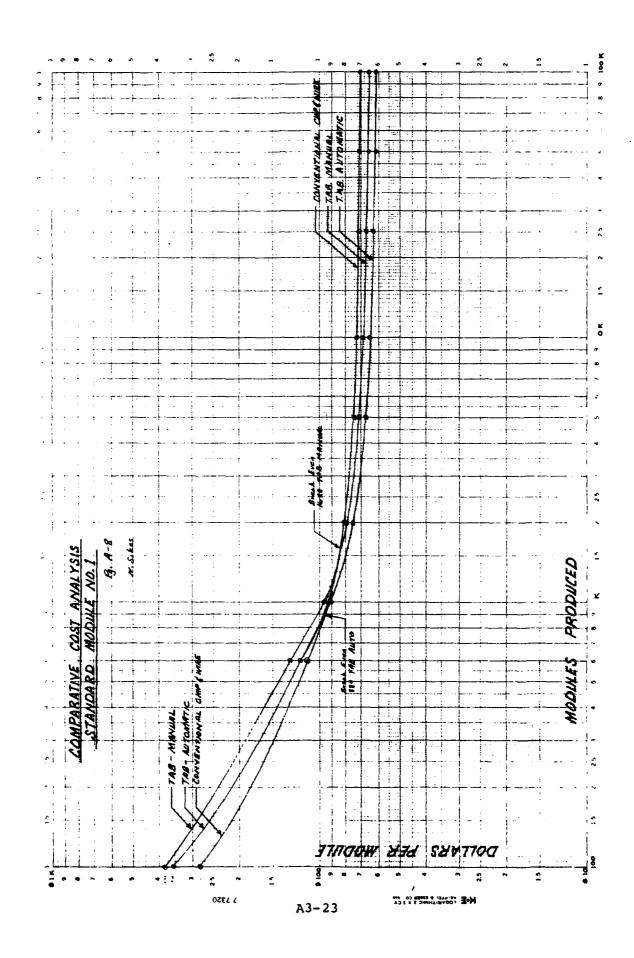
TOTAL MATERIAL COST

STANDARD MODULE NO. 1 - MANUAL T.A.B. PROCESSES

RECURRING LABOR:					COST
PROCESS	PROCESS NO.	뜅	COST FORMULA	<u>LA</u>	PER
Thick Film Printing	C-1	Reff.	TAB	Automatic	\$ 0.21
Component Mount	C-2	=	=	=	0.38
r Mount	C-3	=	=	*	0.10
ding	C-4	=	=	-	0.85
aration	T-1	=	=	-	0.34
Inner Lead Bonding	T-2-M	\$17.95 x	.0200 x	7	2.51
Chin Test	Ė	Ŋ		7	1.04
)			.0028 x	7	0.35
Outer Lead Bonding	Ľ	S	.0083 x	7	1.04
nspect & Rework	£-	Reff.	TAB	Automatic	2.51
nspect & Rework		=	=	=	•
;;;;;;;;;;;;;;;;;;;;;;;;;;;;;;;;;;;;;;		=	:	:	3,08
Test		=	=	=	0.36
Trouble Shoot	۰- د-	=	=	=	•
	T-7	=	=	2	0.64
In	C-10	3.	=	=	0.55
ge Test	[-J	:	=	=	90.0
Seal Package	C-12	:	=	=	0.29
			TOTAL	TOTAL RECURRING COST	= \$20.61 TOTAL
					COST
NON-RECURRING:	(Reff.	TAB Automatic)	_		\$29,291
					COST PER MODULE
MATERIAL COSTS:	(Reff.	TAB Automatic)			\$44.72

STANDARD MODULE NO.1

	Total Cost/ Module	\$44.72 \$29.356	328.24	129,91	94.68	79,98	71.19	68.26	66.50	65.91	65.68	
	¥ 6										>	
T.A.BMANUAL	Non	\$29,291,00	292.91	58.58	29.29	14.65	5.86	2.93	1.17	. 58	29	
T	Recur	\$20.61									->	
	Total Cost/ Module	\$29,352	354.07	119.74	90.45	75.81	67.02	64.09	62,33	61.74	61.45	
MTIC	Mat.	i									 >	
T.A.BAUTOMATIC	Non Pecurring	\$29,291.00	292.91	58.58	29.29	14.65	5.86	2.93	1.17	.58	. 29	
	Recur.	\$16.44									->	
WIRE	Total Cost/ Module	\$21,190	281,55	112.59	91.47	80.91	74.57	72.46	71.19	70.77	70.56	
CHIP &	Mat.	\$40.38 \$21,19		-							->	
CONVENTIONAL CHIP &	Non Recurr.	\$21,120.00	211.20	42.24	21.12	10.56	4.22	2.11	.84	.42	.21	
OO	Recur.	\$29.97									→	
	No.Units	rl .	100	200	1000	2000	2000	10000	25000	20000	100000	



STANDARD MODULE NO. 2 - CONVENTIONAL CHIP & WIRE

RECURRING LABOR COSTS:

		COST/ MODULE
C-1 C-2 C-3 C-4	\$17.95 (.0012+(.0019x5)+(.0014x3)) \$17.95 (.0008+(.0023x18)+(.0039x52 \$17.95 (.0008+(.0023x9(+(.0039x24)) \$17.95 (.0050+(.0009x106)+(.001x52))	()) 4.40 2.07
C-6 C-7 C-8 C-9 C-10 C-11	\$17.95 ((.0146x52)+(.0011x584) \$17.95 ((3.5÷6)+.0048) \$17.95 x .02 \$17.95 x 16.0 x 1.17 \$17.95 x .2000 x 5.644 \$10.56 x 1.17 \$0.36 x 1.17	25.16 10.56 0.36 336.02 20.26 12.36 0.42 0.29
C-12	TOTAL RECURRING COST=	\$418.89
ITEM NO.	COST FORMULA	NON RECURRING
	\$15.00/Layer x 8 Layers \$0.15/Wire x 584 Wires \$3000/IC x 32 IC	\$ 120 88 96,000
	TOTAL NON-RECURRING	\$96,208
MAT. NO.	COST FORMULA	NON RECURRING
M-2 M-3 M-6 M-7 M-8 M-9 M-10 M-11	\$0.75/sub x 1 sub/Module \$1.00/IC x 32 IC/Module \$1.00/chip x 20 chips/Module \$1.00/ cap x 24 caps/Module \$0.01/Wire x 584 wires/Module \$0.90/Print x 8 Layers/Module \$9.75 x 1 Pkg/Module \$3.75 x 1 Pkg/Module	\$ 0.75 32.00 20.00 24.00 5.84 7.20 9.75 3.75
	NO. C-1 C-2 C-3 C-4 C-5 C-6 C-7 C-8 C-9 C-10 C-11 C-12 ITEM NO. NR-1 NR-2 NR-9 MAT. NO. M-2 M-3 M-6 M-7 M-8 M-9 M-10	C-1 \$17.95 (.0012+(.0019x5)+(.0014x3)) C-2 \$17.95 (.0008+(.0023x18)+(.0039x52) C-3 \$17.95 (.0008+(.0023x9(+(.0039x24) C-4 \$17.95 (.0050+(.0009x106)+(.001x52) (.00046x584)) C-5 \$17.95 (.0146x52)+(.0011x584) C-6 \$17.95 ((.0146x52)+(.0011x584)) C-7 \$17.95 x .02 C-8 \$17.95 x .02 C-8 \$17.95 x .02 C-8 \$17.95 x .02 C-9 \$17.95 x .2000 x 5.644 C-10 \$10.56 x 1.17 C-11 \$0.36 x 1.17 C-12 \$17.95 x .016 TOTAL RECURRING COST= ITEM NO. COST FORMULA NR-1 \$15.00/Layer x 8 Layers NR-2 \$0.15/Wire x 584 Wires NR-9 \$3000/IC x 32 IC TOTAL NON-RECURRING MAT. NO. COST FORMULA M-2 \$0.75/sub x 1 sub/Module M-3 \$1.00/IC x 32 IC/Module M-6 \$1.00/chip x 20 chips/Module M-7 \$1.00/ cap x 24 caps/Module M-7 \$1.00/ cap x 24 caps/Module M-8 \$0.01/Wire x 584 wires/Module M-9 \$0.90/Print x 8 Layers/Module M-9 \$0.90/Print x 8 Layers/Module M-10 \$9.75 x 1 Pkg/Module M-11 \$3.75 x 1 Pkg/Module

STANDARD MODULE NO. 2 - AUTOMATIC T.A.B. PROCESSES

PROCESS No. COST FORMULA PER MODULE	RECURRING LABOR:			000m
PROCESS		PROCESS		
Component Mount	PROCESS		COST FORMULA	
(.00046x225)) 2.66 Chip Separation T-1 \$17.95x.0027x32 1.55 Inner Lead Bonding T-2-A \$17.95x.0010x32 .57 Chip Test T-3-A \$17.95x.0010x32 .57 Chip Test T-3-A \$17.95x.0028x32 1.61 Framing T-4-A \$17.95x.0003x32 1.7 Outer Lead Bonding T-5-A \$17.95x.0003x32 1.15 Visual Inspect & Rework T-6 \$17.95x.0020x32 1.15 Visual Inspect \$ Rework T-6 \$17.95x.0020x32 1.15 Visual Inspect \$ Rework T-6 \$17.95x.0146x32)+(.0003x359)) 10.32 Visual Inspect \$ Rework T-6 \$17.95x.0146x32)+(.0003x359)) 10.32 Visual Inspect \$ Rework T-6 \$17.95x.01.46x32)+(.0001x225)) 9.68 Burn-In C-6 \$17.95x.02 0.36 Trouble Shoot C-8 \$17.95x.02 0.36 Trouble Shoot C-8 \$17.95x.02 0.36 Trouble Shoot C-8 \$17.95x.02 0.356 Trouble Shoot C-8 \$17.95x.02 0.356 Tebrack T-7 \$17.95x.000x.82 2.94 Re Burn-In C-10 \$10.56x1.17 12.36 Re Package Test C-11 \$0.36x1.17 12.36 Re Package Test C-12 \$17.95x.016 0.29 TOTAL RECURRING COST \$219.51 NON-RECURRING COSTS: ITEM NO. COST FORMULA RECURRING Thick Film Screens NR-1 \$15.00/Layer x 8 Layers \$120 NON-RECURRING COSTS: ITEM NO. COST FORMULA RECURRING Thermode NR-2 \$0.15/Wire x 225 Wires 34 Tead Frame/Mask Design NR-3 \$500/IC Type x 11 IC Types 5,500 Masks NR-4 \$720/IC Type x 11 IC Types 5,500 Thermode NR-5 \$295 x 11 3,245 Test Cabling NR-6 \$50 x 11 5,000 IC Test Program NR-7 \$950 x 11 10,450 IC Test Fixturing NR-8 \$215 x 11 2,365 Pkg. Level Testing,	Component Mount Capacitor Mount	C-2 C-3	\$17.95 (0008+(.0023x7)+(.0039x20)) \$17.95 (0008+(.0023x9)+(.0039x24))	1.70
NON-RECURRING COSTS: ITEM NON RECURRING COST Security	Chip Separation Inner Lead Bonding Chip Test Framing Outer Lead Bonding Visual Inspect & Rework Visual Inspect \$ Rework Burn-In Package Test Trouble Shoot Rework Re Burn-In	T-2-A T-3-A T-4-A T-5-A T-6 C-5 C-6 C-7 C-8 T-7 C-10	(.00046x225)) \$17.95x.0027x32 \$17.95x.0010x32 \$17.95x.0028x32 \$17.95x.0003x32 \$17.95x.0020x32 \$17.95x((.0146x32)+(.0003x359)) \$17.95x((.0146x20)+(.0011x225)) \$17.95x((3.5÷6)+.0048) \$17.95x.02 \$17.95x.02 \$17.95x.2000x.82 \$10.56x1.17	1.55 .57 1.61 .17 1.15 10.32 9.68 10.56 0.36 160.83 2.94 12.36
NON-RECURRING COSTS: ITEM NO. COST FORMULA NON RECURRING Thick Film Screens NR-1 \$15.00/Layer x 8 Layers \$ 120 Program Auto Wirebonder NR-2 \$0.15/Wire x 225 Wires 34 Lead Frame/Mask Design NR-3 \$500/IC Type x 11 IC Types 5,500 Masks NR-4 \$720/IC Type x 11 7,920 Thermode NR-5 \$295 x 11 7,920 Test Cabling NR-6 \$50 x 11 550 IC Test Program NR-7 \$950 x 11 10,450 IC Test Fixturing NR-8 \$215 x 11 2,365 Pkg. Level Testing, *** **** **** ****				
ITEM NO. COST FORMULA RECURRING			TOTAL RECURRING COST =	\$219.51
Program Auto Wirebonder NR-2 \$0.15/Wire x 225 Wires 34 Lead Frame/Mask Design NR-3 \$500/IC Type x 11 IC Types 5,500 Masks NR-4 \$720/IC Type x 11 7,920 Thermode NR-5 \$295 x 11 3,245 Test Cabling NR-6 \$50 x 11 550 IC Test Program NR-7 \$950 x 11 10,450 IC Test Fixturing NR-8 \$215 x 11 2,365 Pkg. Level Testing, 2 2,365			COST FORMULA	
	Program Auto Wirebonder Lead Frame/Mask Design Masks Thermode Test Cabling IC Test Program IC Test Fixturing Pkg. Level Testing,	NR-2 NR-3 NR-4 NR-5 NR-6 NR-7 NR-8	\$0.15/Wire x 225 Wires \$500/IC Type x 11 IC Types \$720/IC Type x 11 \$295	34 5,500 7,920 3,245 550 10,450 2,365

TOTAL NONRECURRING = \$126,184

STANDARD MODULE NO. 2 - AUTOMATIC TAB PROCESSES

MATERIAL	MATERIAL NO.	COST FORMULA	MATERIAL
Substrate 2" x 2"	M-2	<pre>\$0.75/sub x 1 sub/module</pre>	\$ 0.75
Integrated Circuits with Bumps	M-4	\$1.10/IC x 32 IC/module	35.20
Lead Frame	M-5	$$0.70/IC \times 32 IC/module$	22.40
Resistor Chip	M-6	\$1.00/chip x 20 chips/module	20.00
Capacitor	M-7	\$1.00/cap x 24 caps/module	24.00
Gold Wire	M-8	<pre>\$0.01/wire x 225 wires/module</pre>	2.25
Thick Film Ink	6-M	\$0.90/print x 8 Layers	7.20
Package	M-10	\$9.75/pkg x 1/module	9.75
Lid	M-11	\$3.75/lid x 1/module	3.75

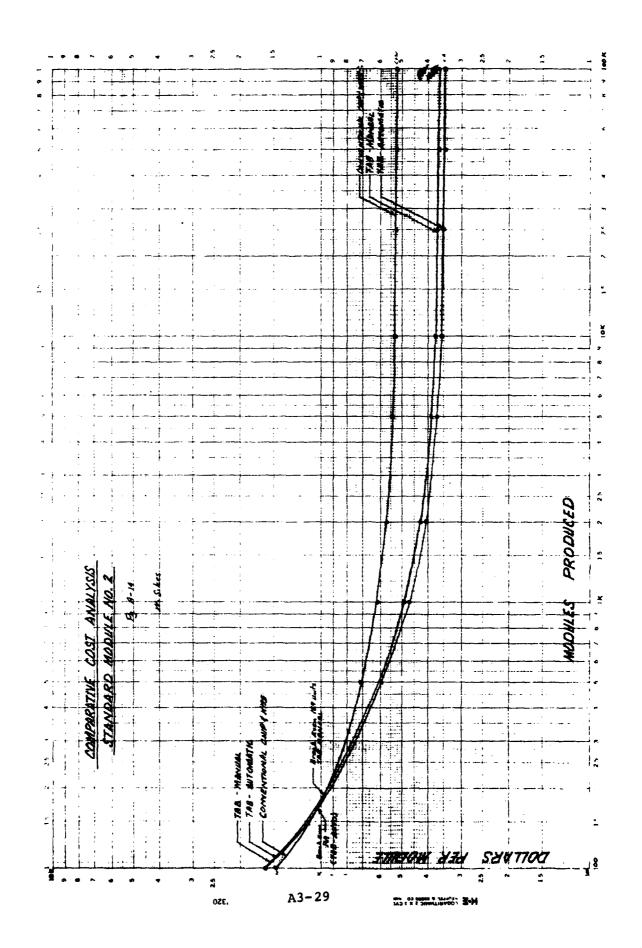
TOTAL MATERIAL COST

STANDARD MODULE NO. 2 - MANUAL T.A.B. PROCESSES

RECURRING LABOR PROCESS	PROCESS NO.	COST FORMULA	COST PER MODULE
Thick Film Printing Component Mount Capacitor Mount Wire Bonding Chip Separation Inner Lead Bonding Chip Test Framing Outer Lead Bonding Visual Inspect & Rework Visual Inspect & Rework Burn-in Pakcage Test Trouble Shoot Rework Re Burn-in Re Package Test Seal Package	C-1 Reff. C-2 " C-3 " C-4 " T-1 " T-2-M \$17.95 x T-3-M \$17.95 x T-4-M \$17.95 x T-5-M \$17.95 x T-5-M \$17.95 x T-5-M \$17.95 x T-6 Reff. C-5 " C-6 " C-7 " C-8 " T-7 " C-10 " C-11 " C-12 "	.0083 x 32 0028 x 32	\$ 0.27 1.70 2.07 2.66 1.55 11.49 4.77 1.61 4.77 10.32 9.68 10.56 0.36 160.83 2.94 12.36 0.42 0.29
	TOTAL	RECURRING COST = .	\$238.65
NON-RECURRING:	(Reff. TAB	Automatic) \$	TOTAL COST 126,184.
MATERIAL COSTS:	(Reff. TAB	Automatic)	COST PER MODULE \$125.30

STANDARD MODULE NO. 2

	Total Cost/ Module	\$126,548	1625.79	616.32	490.13	427.04	389.19	376.57	369.00	366.47	365.21
- Manual	Mat.	\$125.30							-		→
T.A.B.	Non Recurr.Recurring	\$126,184.\$125.30	1261.84	252.37	126.18	63.09	25.24	12.62	5.05	2.52	1.26
	Recurr.	\$238.65									\rightarrow
ic	Total Cost/ Module	\$126,529\$238.65	1606.65	597.18	470.99	407.90	370.05	357,43	349.86	341.33	346.07
- Automatic	Mat.	\$125,30			,						\rightarrow
T.A.B	Non Recurring	\$126,184.\$125.30	1261.84	252.37	126.18	63.09	25.24	12.62	5.05	2.52	1.26
	Recurr.	\$219.51									\rightarrow
Wire	Total Cost/ Module	\$96,730	1484.26	714.60	618.39	570.28	541.42	531.80	526.03	524.10	523.14
Chip &	Mat.	\$103,29									→
Conventional Chip & Wire	Non Recur.	18418,89496,208.\$103,29	962.08	192.42	96.21	48.10	19.24	9.62	3.85	1.92	96.
Conve	Recur.	1418.89									\rightarrow
	No.Units	1	100	200	1000	2000	2000	10000	25000	20000	100,000



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